

# mos integrated circuit $\mu$ PD78F0058,78F0058Y

#### 8-BIT SINGLE-CHIP MICROCONTROLLERS

#### **DESCRIPTION**

The  $\mu$ PD78F0058 is a product of the  $\mu$ PD780058 Subseries in the 78K/0 Series and equivalent to the  $\mu$ PD780058 with a flash memory in place of internal ROM. This device is incorporated with a flash memory which can be programmed without being removed from the substrate.

The  $\mu$ PD78F0058Y is a products based on the  $\mu$ PD78F0058, with an I<sup>2</sup>C bus interface supporting multimaster.

Functions are described in detail in the following user's manuals, which should be read when carrying out design work.

 $\mu$ PD780058, 780058Y Subseries User's Manual :U12013E 78K/0 Series User's Manual Instruction :U12326E

#### **FEATURES**

• Pin-compatible with mask ROM version (except VPP pin)

Flash memory : 60 Kbytes<sup>Note 1</sup>
 Internal high-speed RAM : 1024 bytes
 Internal expansion RAM : 1024 bytes<sup>Note 2</sup>

• Buffer RAM : 32 bytes

• Power supply voltage : VDD = 2.7 to 5.5 V

Notes 1. The flash memory capacity can be changed with the memory size switching register (IMS).

2. The internal expansion RAM capacity can be changed with the internal expansion RAM size switching register (IXS).

Remark For the differences between the flash memory versions and the mask ROM versions, refer to

1. DIFFERENCES BETWEEN  $\mu$ PD78F0058, 78F0058Y, AND MASK ROM VERSION.

#### **APPLICATION FIELDS**

Car audio systems, cellular phones, pagers, printers, AV equipment, cameras, PPCs, vending machines, etc.

The information in this document is subject to change without notice. Before using this document, please confirm that this is the latest version.

Not all devices/types available in every country. Please check with local NEC representative for availability and additional information.

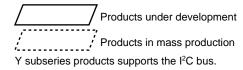


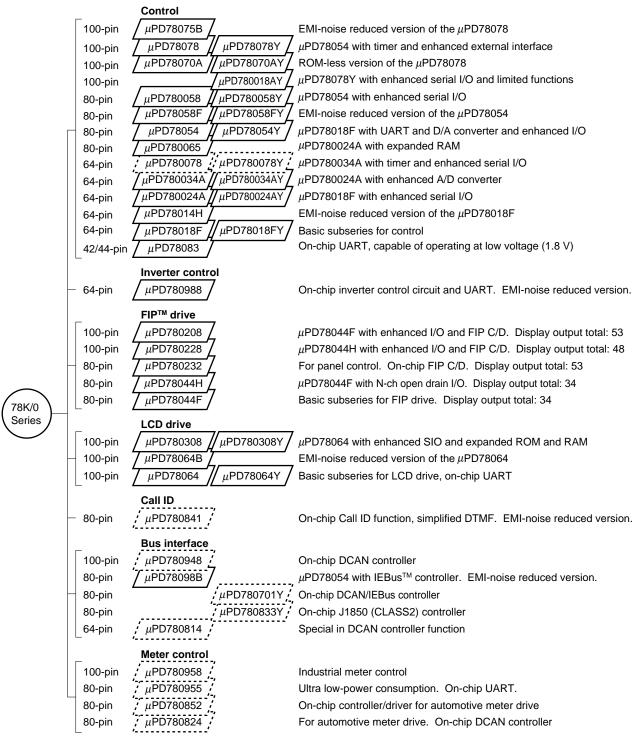
## ORDERING INFORMATION

	Part Number	Package
	μPD78F0058GC-8BT	80-pin plastic QFP (14 × 14 mm)
	μPD78F0058GK-BE9	80-pin plastic TQFP (fine pitch) (12 $\times$ 12 mm, resin thickness 1.05 mm)
*	$\mu$ PD78F0058GK-9EU <sup>Note</sup>	80-pin plastic TQFP (fine pitch) (12 $\times$ 12 mm, resin thickness 1.0 mm)
	$\mu$ PD78F0058YGC-8BT	80-pin plastic QFP $(14 \times 14 \text{ mm})$
	$\mu$ PD78F0058YGK-BE9	80-pin plastic TQFP (fine pitch) (12 $\times$ 12 mm, resin thickness 1.05 mm)
*	$\mu$ PD78F0058YGK-9EU <sup>Note</sup>	80-pin plastic TQFP (fine pitch) (12 $\times$ 12 mm, resin thickness 1.0 mm)
	Note Under development	

#### **★** 78K/0 SERIES LINEUP

The products in the 78K/0 Series are listed below. The names enclosed in boxes are subseries name.







The major functional differences among the subseries are listed below.

	Function	ROM		Tir	ner		8-Bit	10-Bit	8-Bit	Serial	1/0	V <sub>DD</sub> MIN.	External
Subseries Name		Capacity	8-bit	16-bit	Watch	WDT	A/D	A/D	D/A	Interface	I/O	Value	Expansion
Control	μPD78075B	32 K to 40K	4 ch	1 ch	1 ch	1 ch	8 ch	_	2 ch	3 ch (UART: 1 ch)	88	1.8 V	√
	μPD78078	48 K to 60K											
	μPD78070A	-									61	2.7 V	
	μPD780058	24 K to 60 K	2 ch							3 ch (time-division UART: 1 ch)	68	1.8 V	
	μPD78058F	48 K to 60 K								3 ch (UART: 1 ch)	69	2.7 V	
	μPD78054	16 K to 60 K										2.0 V	
	μPD780065	40 K to 48 K							_	4 ch (UART: 1 ch)	60	2.7 V	
	μPD780078	48 K to 60 K		2 ch			_	8 ch		3 ch (UART: 2 ch)	52	1.8 V	
	μPD780034A	8 K to 32 K		1 ch						3 ch (UART: 1 ch)	51		
	μPD780024A						8 ch	_					
	μPD78014H									2 ch	53		
	μPD78018F	8 K to 60 K											
	μPD78083	8 K to 16 K		_	_					1 ch (UART: 1 ch)	33		_
Inverter control	μPD780988	16 K to 60 K	3 ch	Note	_	1 ch	_	8 ch	_	3 ch (UART: 2 ch)	47	4.0 V	√
FIP	μPD780208	32 K to 60 K	2 ch	1 ch	1 ch	1 ch	8 ch	_	_	2 ch	74	2.7 V	-
drive	μPD780228	48 K to 60 K	3 ch	_	_					1 ch	72	4.5 V	
	μPD780232	16 K to 24 K					4 ch			2 ch	40		
	μPD78044H	32 K to 48 K	2 ch	1 ch	1ch		8 ch			1 ch	68	2.7 V	
	μPD78044F	16 K to 40 K								2 ch			
LCD drive	μPD780308	48 K to 60 K	2 ch	1 ch	1ch	1 ch	8 ch	-	-	3 ch (time-division UART: 1 ch)	57	2.0 V	-
	μPD78064B	32 K								2 ch (UART: 1 ch)			
	μPD78064	16 K to 32 K											
Call ID	μPD780841	24 K to 32 K	1 ch	1 ch	1 ch	1 ch	2 ch	_	_	2 ch (UART: 1 ch)	57	2.7 V	-
Bus	μPD780948	60 K	2 ch	2 ch	1 ch	1 ch	8 ch	_	_	3 ch (UART: 1 ch)	79	4.0 V	<b>√</b>
interface	μPD78098B	40 K to 60 K		1 ch					2 ch		69	2.7 V	-
supported	μPD780814	32 K to 60 K		2 ch			12 ch		_	2 ch (UART: 1 ch)	46	4.0 V	
Meter	μPD780958	48 K to 60 K	4 ch	2 ch	-	1 ch	_	_	_	2 ch (UART: 1 ch)	69	2.2 V	_
control	μPD780955	40 K	6 ch	1 ch			1 ch			2 ch (UART: 2 ch)	50		
	μPD780852	32 K to 40 K	3 ch		1 ch		5 ch			3 ch (UART: 1 ch)	56	4.0 V	]
	μPD780824	32 K to 60 K								2 ch (UART: 1 ch)	59	4.0 V	

Note 16-bit timer: 2 channels 10-bit timer: 1 channel



The major functional differences among the Y subseries are shown below.

	Function	ROM Capacity	Configuration of Serial Inte	rface	I/O	VDD MIN.
Subserie	es Name					Value
Control	μPD78078Y	48 K to 60 K	3-wire/2-wire/I <sup>2</sup> C	: 1 ch	88	1.8 V
	μΡD78070ΑΥ	_	3-wire with automatic transmit/receive function 3-wire/UART	: 1 ch	61	2.7 V
	μPD780018AY	48 K to 60 K	3-wire with automatic transmit/receive function Time-division 3-wire I <sup>2</sup> C bus (multimaster supported)	: 1 ch : 1 ch : 1 ch	88	
	μPD780058Y	24 K to 60 K	3-wire/2-wire/I <sup>2</sup> C 3-wire with automatic transmit/receive function 3-wire/time-division UART	: 1 ch : 1 ch : 1 ch	68	1.8 V
	μPD78058FY	48 K to 60 K	3-wire/2-wire/l <sup>2</sup> C 3-wire with automatic transmit/receive function	: 1 ch	69	2.7 V
	μPD78054Y	16 K to 60 K	3-wire/UART	: 1 ch		2.0 V
	μPD780078Y	48 K to 60 K	3-wire UART 3-wire/UART I <sup>2</sup> C bus (multimaster supported)	: 1 ch : 1 ch : 1 ch : 1 ch	52	1.8 V
	μPD780034AY	8 K to 32 K	UART	: 1 ch	51	1.8 V
	μPD780024AY		3-wire I <sup>2</sup> C bus (multimaster supported)	: 1 ch : 1 ch		
	μPD78018FY	8 K to 60 K	3-wire/2-wire/I <sup>2</sup> C 3-wire with automatic transmit/receive function	: 1 ch : 1 ch	53	
LCD drive	μPD780308Y	48 K to 60 K	3-wire/2-wire/I <sup>2</sup> C 3-wire/time-division UART 3-wire	: 1 ch : 1 ch : 1 ch	57	2.0 V
	μPD78064Y	16 K to 32 K	3-wire/2-wire/l <sup>2</sup> C 3-wire/UART	: 1 ch : 1 ch		

Remark The functions other than the serial interface are common to the Subseries without Y.

### **OVERVIEW OF FUNCTIONS**

	Product Name	μPD78F0058	μPD78F0058Y				
Item							
Internal	Flash memory	60 Kbytes					
memory	High-speed RAM	1,024 bytes					
	Buffer RAM	32 bytes					
	Expanded RAM	1,024 bytes					
Memory sp	ace	64 Kbytes					
General reg	gisters	8 bits $\times$ 32 registers (8 bits $\times$ 8 registers $\times$ 4	banks)				
Minimum instruction	When main system clock is selected	0.4 μs/0.8 μs/1.6 μs/3.2 μs/6.4 μs/12.8 μs (@	25.0 MHz operation)				
execution time	When subsystem clock is selected	122 μs (@32.768 kHz operation)					
Instruction	set	<ul> <li>16-bit operation</li> <li>Multiply/divide (8 bits × 8 bits, 16 bits ÷ 8 bits)</li> <li>Bit manipulation (set, reset, test, Boolean operation)</li> <li>BCD adjust, etc.</li> </ul>					
I/O ports		Total: 68					
A/D conver	ter	8-bit resolution × 8 channels (V <sub>DD</sub> = 2.7 to 5.5 V)					
D/A conver	ter	• 8-bit resolution × 2 channels (V <sub>DD</sub> = 2.7 to 5.5 V)					
Serial inter	face	3-wire serial I/O/SBI/2-wire serial	3-wire serial I/O/2-wire serial I/O/				
		I/O mode selectable: 1 channel     3-wire serial I/O mode (automatic data transmit/receive function for up to 32 bytes provided on chip): 1 channel     3-wire/serial I/O/UART mode (time division transfer function provided on chip) selectable: 1 channel					
Timers		16-bit timer/event counter: 1 channel     8-bit timer/event counter: 2 channels     Watch timer: 1 channel     Watchdog timer: 1 channel					
Timer outp	uts	3 (14-bit PWM output × 1)					
Clock outpo	ut	19.5 kHz, 39.1 kHz, 78.1 kHz, 156 kHz, 313 kHz, 625 kHz, 1.25 MHz, 2.5 MHz, 5.0 MHz (@5.0 MHz operation with main system clock) 32.768 kHz (@32.768 kHz operation with subsystem clock)					
Buzzer out	put	1.2 kHz, 2.4 kHz, 4.9 kHz, 9.8 kHz (@5.0 MHz operation with main system clock)					
Vectored	Maskable	Internal: 13, External: 6					
interrupt	Non-maskable	Internal: 1					
sources	Software	1					
Test inputs		Internal: 1, External: 1					
Supply volt	age	V <sub>DD</sub> = 2.7 to 5.5 V					
Operating a	ambient temperature	$T_A = -40 \text{ to } +85^{\circ}\text{C}$					
Package	-	80-pin plastic QFP (14 × 14 mm)     80-pin plastic TQFP (fine pitch) (12 × 12 mm, resin thickness 1.05 mm)     80-pin plastic TQFP (fine pitch) (12 × 12 mm, resin thickness 1.0 mm)					

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#### 1. PIN CONFIGURATION (TOP VIEW)

- 80-pin plastic QFP (14  $\times$  14 mm)  $\mu$ PD78F0058GC-8BT, 78F0058YGC-8BT
- 80-pin plastic TQFP (fine pitch) (12  $\times$  12 mm, resin thickness 1.05 mm)  $\mu$ PD78F0058GK-BE9, 78F0058YGK-BE9
- \* 80-pin plastic TQFP (fine pitch) (12  $\times$  12 mm, resin thickness 1.0 mm)  $\mu$ PD78F0058GK-9EU<sup>Note</sup>, 78F0058YGK-9EU<sup>Note</sup>

Note Under development P00/INTP0/T100 P04/INTP<sup>2</sup> P10/ANI0 XT1/P07 × Q 80 79 78 77 76 75 74 73 72 71 70 69 68 67 66 65 64 63 62 61 60 P15/ANI5 O → RESET 2 P16/ANI6 O- $\bigcirc$ 59 -O P127/RTP7 3 P17/ANI7 ○ 58 P126/RTP6 AVss O 4 57 -O P125/RTP5 P130/ANO0 ○-5 56 -O P124/RTP4 P131/ANO1 O-6 55 ► P123/RTP3 AV REF1 7 54 -○ P122/RTP2 8 P70/SI2/RxD0 ○-53 -○ P121/RTP1 -O P120/RTP0 P71/SO2/TxD0 ○ 9 52 P72/SCK2/ASCK ○-10 51 →○ P37 P20/SI1 O-11 50 -○ P36/BUZ P21/SO1 O-12 49 →○ P35/PCL P22/SCK1 O-13 48 -○ P34/TI2 P23/STB/TxD1 ○-14 47 -○ P33/TI1 P24/BUSY/RxD1 ○-15 46 -○ P32/TO2 P25/SI0/SB0 [/SDA0] O-16 45 -○ P31/TO1 17 P26/SO0/SB1 [/SDA1] O-44 →○ P30/TO0 P27/SCK0 [/SCL] ○-18 43 -O P67/ASTB 19 42 ►O P66/WAIT P40/AD0 ○-P41/AD1 O--○ P65/WR P61 P62 0-Vss<sub>1</sub> P60 --42/AD2 O--944/AD4 ○-->46/AD6 ⊖-P50/A8 -P51/A9 🕞 P52/A10 0-P53/A11 0-P54/A12 0-P55/A13 0-P56/A14 0-P57/A15 0-P47/AD7 -P64/RD -

- Cautions 1. Connect the VPP pin directly to Vsso or Vss1 in normal operation mode.
  - 2. Connect the AVss pin to Vsso.
- **Remarks 1.** [ ]:  $\mu$ PD78F0058Y only.
  - 2. When the microcontroller is used in applications where the noise generated inside the microcontroller needs to be reduced, the implementation of noise reduction measures, such as supplying voltage to VDD0 and VDD1 individually and connecting Vss0 and Vss1 to different ground lines, is recommended.



#### PIN IDENTIFICATION

P40 to P47

: Port 4

AD0 to AD7 : Address/Data Bus RESET : Reset

ANI0 to ANI7 : Analog Input RTP0 to RTP7 : Real-Time Output Port

ANO0, ANO1 : Analog Output RxD0, RxD1 : Receive Data

ASCK : Asychronous Serial Clock SB0, SB1 : Serial Bus

ASTB : Address Strobe SCK0 to SCK2 : Serial Clock

AVREFO, AVREF1 : Analog Reference Voltage SCL : Serial Clock
AVss : Analog Ground SDAO, SDA1 : Serial Data
BUSY : Busy SI0 to SI2 : Serial Input

BUZ : Buzzer Clock SO0 to SO2 : Serial Output

INTP0 to INTP5 : Interrupt from Peripherals STB : Strobe P00 to P05, P07 : Port 0 : Timer Input TI00, TI01 P10 to P17 : Port 1 TI1, TI2 : Timer Input P20 to P27 : Port 2 TO0 to TO2 : Timer Output P30 to P37 : Port 3 TxD0, TxD1 : Transmit Data

P50 to P57 : Port 5 VPP : Programming Power Supply

VDD0, VDD1

: Power Supply

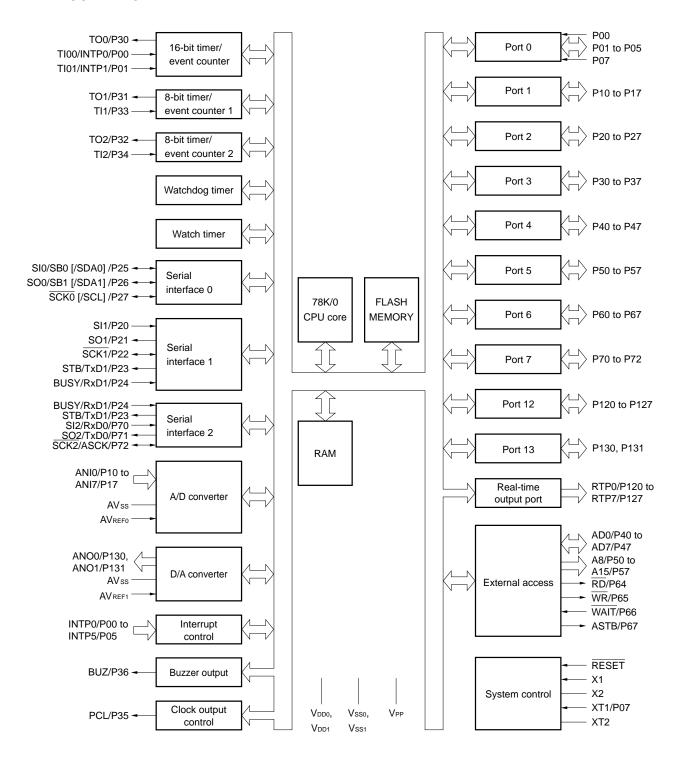
P60 to P67 : Port 6 Vsso, Vsso : Ground P70 to P72 : Port 7 WAIT : Wait

P120 to P127 : Port 12  $\overline{\text{WR}}$  : Write Strobe

P130, P131 : Port 13 X1, X2 : Crystal (Main System Clock)

PCL : Programmable Clock XT1, XT2 : Crystal (Subsystem Clock)

#### 2. BLOCK DIAGRAM



**Remark** [ ]:  $\mu$ PD78F0058Y only.

#### 3. DIFFERENCES BETWEEN $\mu$ PD78F0058, 78F0058Y, AND MASK ROM VERSIONS

The  $\mu$ PD78F0058 and 78F0058Y are products provided with a flash memory which enables on-board reading, erasing, and rewriting of programs with device mounted on target system. The functions of the  $\mu$ PD78F0058 and 78F0058Y (except the functions specified for flash memory and mask option of P60 to P63 pins) can be made the same as those of the mask ROM versions by setting the memory size switching register (IMS) and internal expansion RAM size switching register (IXS).

Table 3-1 shows the differences between the flash memory version ( $\mu$ PD78F0058, 78F0058Y) and the mask ROM versions ( $\mu$ PD780053, 780054, 780055, 780056, 780058, 780053Y, 780054Y, 780055Y,780056Y, and 780058Y).

Table 3-1. Differences between  $\mu$ PD78F0058, 78F0058Y and Mask ROM Versions

	Item	μPD78F0058	μPD78F0058Y	Mask ROM Versions		
				μPD780058 Subseries	μPD780058Y Subseries	
	Internal ROM structure	Flash memory		Mask ROM		
	Internal ROM capacity	60 Kbytes		μPD780053, 780053Y: 24 Kbyte μPD780054, 780054Y: 32 Kbyte μPD780055, 780055Y: 40 Kbyte μPD780056, 780056Y: 48 Kbyte μPD780058, 780058Y: 60 Kbyte		
	Internal expansion RAM capacity	1024 bytes		μPD780053, 7800 μPD780054, 7800 μPD780055, 7800 μPD780056, 7800 μPD780058, 7800	054Y : None 055Y : None	
	Internal ROM capacity changeable/not changeable with memory size switching register (IMS)	Changeable Note	I	Not changeable		
	Internal expansion RAM capacity changeable/not changeable with internal expansion RAM size switching register (IXS)	Changeable Note 2	2	Not changeable		
- [	Supply voltage	V <sub>DD</sub> = 2.7 to 5.5	V	V <sub>DD</sub> = 1.8 to 5.5 \	/	
	IC pin	Not provided		Provided		
	V <sub>PP</sub> pin	Provided		Not provided		
	P60 to P63 pin mask option with internal pull-up resistors	Not provided		Provided		
-	Serial interface (SBI)	Provided	Not provided	Provided	Not provided	
.	Serial interface (I <sup>2</sup> C)	Not provided	Provided	Not provided	Provided	

- Notes 1. Flash memory is set to 60 Kbytes by RESET input.
  - 2. Internal expansion RAM is set to 1024 bytes by RESET input.

Caution The noise resistance and noise radiation differ between flash memory versions and mask ROM versions. When considering the replacement of flash memory versions with mask ROM versions in the process from trial manufacturing to mass production, adequate evaluation should be carried out using CS products (not ES products) of mask ROM versions.

**Remark** Only the  $\mu$ PD780058, 780058Y, 78F0058, and 78F0058Y are provided with IXS.



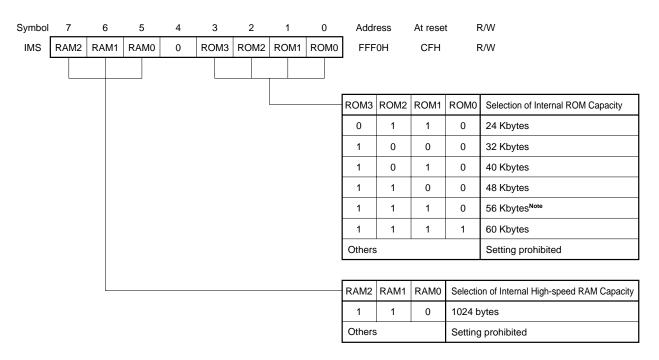
#### 3.1 Memory Size Switching Register (IMS)

This register sets a part of internal memory unused by software. The memory mapping can be made the same as that of mask ROM versions with different types of internal memory (ROM and RAM) by setting the memory size switching register (IMS).

The IMS is set with an 8-bit memory manipulation instruction.

RESET input sets the IMS to CFH.

Figure 3-1. Format of Memory Size Switching Register



Note When using external device expansion function, set the internal ROM capacity to less than 56 Kbytes.

Table 3-2 shows the IMS set value to make the memory mapping the same as those of mask ROM versions.

Table 3-2. Set Value of Memory Size Switching Register

Target Mask ROM Versions	IMS Set Value
μPD780053, 780053Y	C6H
μPD780054, 780054Y	C8H
μPD780055, 780055Y	CAH
μPD780056, 780056Y	ССН
μPD780058, 780058Y	CFH

#### 3.2 Internal Expansion RAM Size Switching Register (IXS)

This register sets the internal expansion RAM capacity by software. The memory mapping can be made the same as that of mask ROM versions with different types of internal expansion RAM by setting the internal expansion RAM size switching register (IXS).

The IXS is set with an 8-bit memory manipulation instruction.

RESET input sets the IXS to 0AH.

Figure 3-2. Format of Internal Expansion RAM Size Switching Register

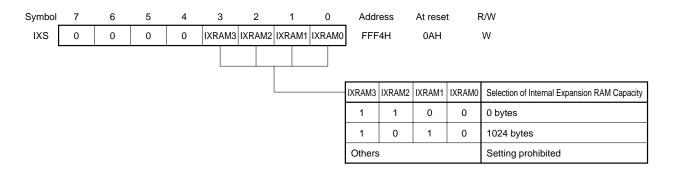


Table 3-3 shows the IXS set value to make the memory mapping the same as those of mask ROM versions.

Table 3-3. Set Value of Internal Expansion RAM Size Switching Register

Target Mask ROM Versions	IMS Set Value
μPD780053, 780053Y	0CH
μPD780054, 780054Y	
μPD780055, 780055Y	
μPD780056, 780056Y	
μPD780058, 780058Y	0AH



#### 4. PIN FUNCTIONS

### 4.1 Port Pins (1/2)

Pin Name	I/O		Function	After Reset	Alternate Function
P00	Input	Port 0	Input only	Input	INTP0/TI00
P01	I/O	7-bit input/output port	Input/output can be specified in 1-bit units.	Input	INTP1/TI01
P02			When used as an input port, an on-chip pull-up		INTP2
P03			resistor can be specified by means of software.		INTP3
P04					INTP4
P05					INTP5
P07 <sup>Note 1</sup>	Input	_	Input only	Input	XT1
P10 to P17	I/O	Port 1 8-bit input/output port Input/output can be spec When used as an input specified by means of so	port, an on-chip pull-up resistor can be	Input	ANI0 to ANI7
P20	I/O	I/O Port 2		Input	SI1
P21		8-bit input/output port		SO1	
P22		Input/output can be spectified When used as an input		SCK1	
P23		specified by means of se		STB/TxD1	
P24				BUSY/RxD1	
P25				SI0/SB0 [/SDA0]	
P26				SO0/SB1 [/SDA1]	
P27					SCK0 [/SCL]
P30	I/O	Port 3		Input	TO0
P31		8-bit input/output port	·	TO1	
P32		Input/output can be spectiment when used as an input in		TO2	
P33		When used as an input port, an on-chip pull-up resistor can be specified by means of software.		TI1	
P34					TI2
P35					PCL
P36					BUZ
P37					-
P40 to P47	I/O		port, an on-chip pull-up resistor can be oftware. The test input flag (KRIF) is set to 1	Input	AD0 to AD7

**Notes 1.** When using the P07/XT1 pins as an input port, set bit 6 (FRC) of the processor clock control register (PCC) to 1. Do not use the on-chip feedback resistor of the subsystem clock oscillator.

2. When using the P10/ANI0 to P17/ANI7 pins as the A/D converter analog input pins, set port 1 to the input mode. At this time, on-chip pull-up resistors are automatically disconnected.

**Remark** [ ]:  $\mu$ PD78F0058Y only.

## 4.1 Port Pins (2/2)

Pin Name	I/O		Function	After Reset	Alternate Function
P50 to P57	I/O	Port 5 8-bit input/output port LEDs can be driven directly. Input/output can be specified When used as an input port, a means of software.	in 1-bit units. In on-chip pull-up resistor can be specified by	Input	A8 to A15
P60	I/O	I/O Port 6	N-ch open-drain input/output port	Input	-
P61		8-bit input/outport port Input/output can be specified	LEDs can be driven directly.		
P62	ĺ	in 1-bit units.			
P63					
P64			When used as an input port, an on-chip pull-up resistor can be specified by means of software.		RD
P65					WR
P66					WAIT
P67				ASTB	
P70	I/O	Port 7 3-bit input/output port Input/output can be specified in 1-bit units. When used as an input port, an on-chip pull-up resistor can be specified by means of software.			SI2/RxD0
P71					SO2/TxD0
P72					SCK2/ASCK
P120 to P127	I/O	Port 12 8-bit input/output port Input/output can be specified When used as an input port, means of software.	in 1-bit units. on-chip pull-up resistor can be specified by	Input	RTP0 to RTP7
P130, P131	I/O	Port 13 2-bit input/output port Input/output can be specified When used as an input port, a means of software.	in 1-bit units. In on-chip pull-up resistor can be specified by	Input	ANO0, ANO1



## 4.2 Non-Port Pins (1/2)

Pin Name	I/O	Function	After Reset	Alternate Function
INTP0	Input	External interrupt request input for which the valid edge (rising edge,	Input	P00/TI00
INTP1		falling edge, or both rising edge and falling edges) can be specified.		P01/TI01
INTP2				P02
INTP3				P03
INTP4				P04
INTP5				P05
SI0	Input	Serial interface serial data input	Input	P25/SB0 [/SDA0]
SI1				P20
SI2				P70/RxD
SO0	Output	Serial interface serial data output	Input	P26/SB1 [/SDA1]
SO1				P21
SO2				P71/TxD
SB0	I/O	Serial interface serial data input/output	Input	P25/SI0 [/SDA0]
SB1				P26/SO0 [/SDA1]
SDA0		μPD78F0058Y only		P25/SI0/SB0
SDA1				P26/SO0/SB1
SCK0	I/O	Serial interface serial clock input/output		P27 [/SCL]
SCK1				P22
SCK2				P72/ASCK
SCL		μPD78F0058Y only	1	P27/SCK0
STB	Output	Serial interface automatic transmit/receive strobe output	Input	P23/TxD1
BUSY	Input	Serial interface automatic transmit/receive busy input	Input	P24/RxD1
RxD0	Input	Asynchronous serial interface serial data input	Input	P70/SI2
RxD1				P24/BUSY
TxD0	Output	Asynchronous serial interface serial data output	Input	P71/SO2
TxD1				P23/STB
ASCK	Input	Asynchronous serial interface serial clock input	Input	P72/SCK2
TI00	Input	External count clock input to the 16-bit timer (TM0)	Input	P00/INTP0
TI01		Capture trigger signal input to the capture register (CR00)		P01/INTP1
TI1		External count clock input to the 8-bit timer (TM1)	-	P33
TI2		External count clock input to the 8-bit timer (TM2)		P34
TO0	Output	16-bit timer (TM0) output (also used for 14-bit PWM output)	Input	P30
TO1		8-bit timer (TM1) output	-	P31
TO2		8-bit timer (TM2) output	-	P32
PCL	Output	Clock output (for trimming of main system clock and subsystem clock)	Input	P35
BUZ	Output	Buzzer output	Input	P36
RTP0 to RTP7	Output	Real-time output port from which data is output in synchronization with a trigger	Input	P120 to P127
AD0 to AD7	I/O	Lower address/data bus for expanding memory externally	Input	P40 to P47

**Remark** [ ]:  $\mu$ PD78F0058Y only.



## 4.2 Non-Port Pins (2/2)

Pin Name	I/O	Function	After Reset	Alternate Function
A8 to A15	Output	Higher address bus for expanding memory externally	Input	P50 to P57
RD	Output	Strobe signal output for reading from external memory	Input	P64
WR		Strobe signal output for writing to external memory		P65
WAIT	Input	Wait insertion at external memory access	Input	P66
ASTB	Output	Strobe output that externally latches address information output to ports 4 and 5 to access external memory.	Input	P67
ANI0 to ANI7	Input	A/D converter analog input	Input	P10 to P17
ANO0, ANO1	Output	D/A converter analog output	Input	P130, P131
AV <sub>REF0</sub>	Input	A/D converter reference voltage input (also used for analog power supply)	_	_
AV <sub>REF1</sub>	Input	D/A converter reference voltage input	_	-
AVss	-	A/D converter and D/A converter ground potential Use at the same potential as Vsso.	-	_
RESET	Input	System reset input	_	-
X1	Input	Connecting crystal resonator for main system clock oscillation	-	-
X2	_		-	_
XT1	Input	Connecting crystal resonator for subsystem clock oscillation	Input	P07
XT2	_		_	-
V <sub>DD0</sub>	_	Port block positive power supply	-	-
Vsso	_	Port block ground potential	_	-
V <sub>DD1</sub>	ı	Positive power supply (except for port and analog blocks)	_	_
Vss1	_	Ground potential (except for port and analog blocks)	_	_
VPP	-	Setting flash memory programming mode.  Applying high voltage for program write/verify.  Connect directly to Vsso or Vss1 in normal operation mode.	_	_



#### 4.3 Pin I/O Circuits and Recommended Connection of Unused Pins

The input/output circuit type of each pin and recommended connection of unused pins are shown in Table 4-1. For the input/output circuit configuration of each type, see Figure 4-1.

Table 4-1. Input/Output Circuit Type of Each Pin (1/2)

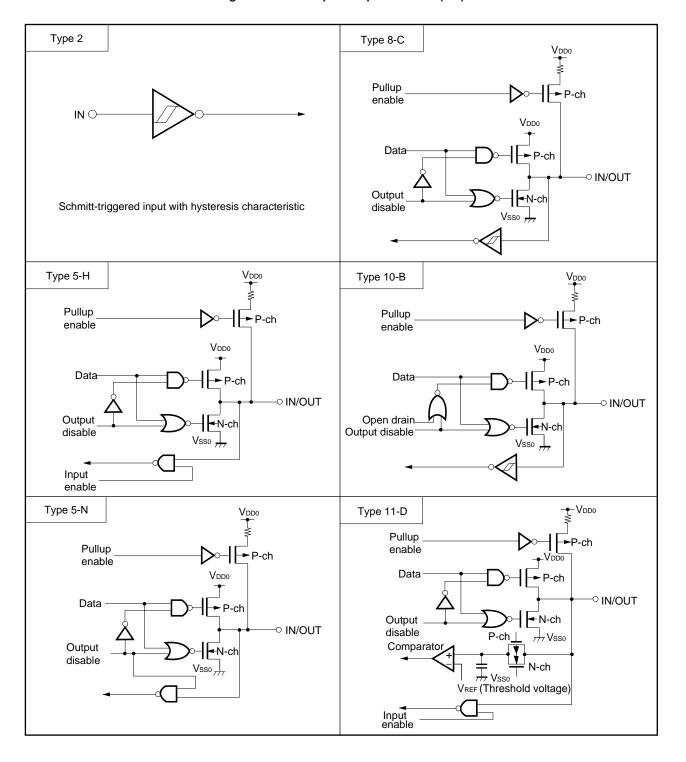
Pin Name	Input/Output Circuit Type	I/O	Recommended Connection
P00/INTP0/TI00	2	Input	Connect to Vsso.
P01/INTP1/TI01	8-C	I/O	Input : Independently connect to Vsso via a resistor.
P02/INTP2			Output : Leave open.
P03/INTP3			
P04/INTP4			
P05/INTP5			
P07/XT1	16	Input	Connect to V <sub>DDO</sub> .
P10/ANI0 to P17/ANI7	11-D	I/O	Input : Independently connect to VDDO or VSSO via a resistor.
P20/SI1	8-C		Output: Leave open.
P21/S01	5-H		
P22/SCK1	8-C		
P23/STB/TxD1	5-H		
P24/BUSY/RxD1	8-C		
P25/SI0/SB0 [/SDA0]	10-B		
P26/SO0/SB1 [/SDA1]	-		
P27/SCK0 [/SCL]	-		
P30/T00	5-H		
P31/TO1			
P32/TO2			
P33/TI1	8-C		
P34/TI2			
P35/PCL	5-H		
P36/BUZ			
P37			
P40/AD0 to P47/AD7	5-N		Input : Independently connect to VDDO via a resistor.  Output : Leave open.
P50/A8 to P57/A15	5-H		Input : Independently connect to VDDO or VSSO via a resistor.  Output : Leave open.
P60 to P63	13-K		Input : Independently connect to VDDO via a resistor.  Output : Leave open.
P64/RD	5-H		Input : Independently connect to VDD0 or VSS0 via a resistor.
P65/WR			Output : Leave open.
P66/WAIT	1		
P67/ASTB	1		

**Remark** [ ]:  $\mu$ PD78F0058Y only.

Table 4-1. Input/Output Circuit Type of Each Pin (2/2)

Pin Name	Input/Output Circuit Type	I/O	Recommended Connection
P70/SI2/RxD0	8-C	I/O	Input : Independently connect to VDD0 or VSS0 via a resistor.
P71/SO2/TxD0	5-H	_	Output : Leave open.
P72/SCK2/ASCK	8-C		
P120/RTP0 to P127/RTP7	5-H		
P130/ANO0, P131/ANO1	12-C		Input : Independently connect to Vsso via a resistor. Output : Leave open.
RESET	2	Input	-
XT2	16	_	Leave open.
AV <sub>REF0</sub>	_		Connect to Vsso.
AVREF1			Connect to VDD0.
AVss	1		Connect to Vsso.
V <sub>PP</sub>	1		Connect directly to Vsso or Vss1.

Figure 4-1. Pin Input/Output Circuits (1/2)



Type 12-C Type 16 Pullup enable Feedback cut-off  $V_{\text{DD0}}$ Data -○ IN/OUT Output disable Vsso , Input enable XT1 XT2 Analog output voltage Type 13-K ⊸IN/OUT Data Output disable - N-ch VDDO  $\overline{\mathsf{RD}}$ Middle-voltage input buffer

Figure 4-1. Pin Input/Output Circuits (2/2)



#### **★** 5. MEMORY SPACE

Figure 5-1 shows the memory map of the  $\mu$ PD78F0058 and 78F0058Y.

FFFFH Special function register (SFR) 256×8 bits FF00H **FEFFH** General registers  $32 \times 8$  bits FEE0H **FEDFH** Internal high-speed RAM 1024×8 bits EFFFH FB00H **FAFFH** Program area Use prohibited FAE0H Data memory **FADFH** 1000H space Internal buffer RAM 0FFFH  $32 \times 8$  bits FAC0H CALLF entry area **FABFH** Use prohibited 0800H F800H 07FFH F7FFH Program area Internal expansion RAM 1024×8 bits H0800 F400H 007FH F3FFH Use prohibited<sup>Note</sup> F000H CALLT table area **EFFF**H 0040H 003FH Program memory Flash memory 61440×8 bits space Vector table area 0000H 0000H

Figure 5-1. Memory Map

**Note** The area between F000H and F3FFH cannot be used when the flash memory size is 60 Kbytes. This area can be used by setting the flash memory size to 56 Kbytes or less with the memory size switching register (IMS).

#### 6. FLASH MEMORY PROGRAMMING

The program memory provided in the  $\mu$ PD78F0058 and 78F0058Y is flash memory.

Writing to a flash memory can be performed without removing the memory from the target system (on-board).

★ Writing is performed connecting the dedicated flash programmer (Flashpro III (part number : FL-PR3, PG-FP3) to the host machine and the target system.

Remark FL-PR3 is a product of Naito Densei Machida Mfg. Co., Ltd.

#### 6.1 Selection of Transmission Mode

Writing to a flash memory is performed using the Flashpro III with a serial transmission mode. One of the transmission mode is selected from those in Table 6-1. The selection of the transmission mode is made by using the format shown in Figure 6-1. Each transmission mode is selected by the number of VPP pulses shown in Table 6-1.

Table 6-1. List of Transmission Mode

Transmission Mode	Channels	Pin	V <sub>PP</sub> Pulses
3-wire serial I/O	3	P27/SCK0 [/SCL]	0
		P26/SO0/SB1 [/SDA1]	
		P25/SI0/SB0 [/SDA0]	
		P22/ <del>SCK1</del>	1
		P21/SO1	
		P20/SI1	
		P72/SCK2/ASCK	2
		P71/SO2/TxD0	
		P70/SI1/RxD0	
UART	2	P71/SO2/TxD0	8
		P70/SI2/RxD0	
		P23/TxD1	9
		P24/RxD1	
Pseudo 3-wire serial I/ONote	1	P32/TO2 (serial clock input/output)	12
		P31/TO1 (serial data output)	
		P30/T00 (serial data input)	

Note Serial transmission is performed by controlling the port using software.

Caution Select a communication mode always using the number of VPP pulses shown in Table 6-1.

**Remark** [ ]:  $\mu$ PD78F0058Y only.

VDD VDD (

Figure 6-1. Format of Transmission Mode Selection

#### **★** 6.2 Function of Flash Memory Programming

Vss

RESET

Operations such as writing to a flash memory are performed by various command/data transmission and reception operations according to the selected transmission mode. Table 6-2 shows major functions of flash memory programming.

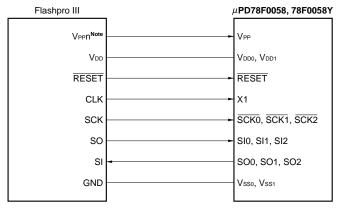
Table 6-2. Major Functions of Flash Memory Programming

Functions	Descriptions
Batch delete	Deletes the entire memory contents.
Batch blank check	Checks the deletion status of the entire memory.
Data write	Performs write to the flash memory based on the write start address and the number of data to be written (number of bytes).
Batch verify	Compares the entire memory contents with the input data.

#### ★ 6.3 Connection of Flashpro III

The connection of the Flashpro III and the  $\mu$ PD78F0058 and 78F0058Y differs according to the transmission mode (3-wire serial I/O, UART, pseudo 3-wire). The connection for each transmission mode is shown in Figures 6-2 to 6-4.

Figure 6-2. Connection of Flashpro III for 3-wire Serial I/O Mode



**Note** n = 1, 2

Figure 6-3. Connection of Flashpro III for UART Mode

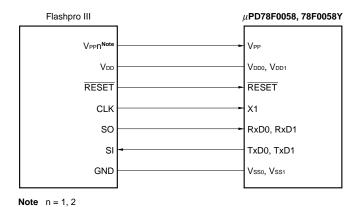
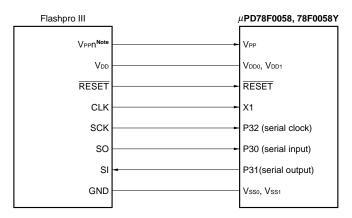


Figure 6-4. Connection of Flashpro III for Pseudo 3-wire Serial I/O Mode



Note n = 1, 2

#### 6.4 Example of Settings for Flashpro III (PG-FP3)

Make the following setting when writing to flash memory using Flashpro III (PG-FP3)

- <1> Load the parameter file.
- <2> Select serial mode and serial clock using the type command.
- <3> An example of the settings for the PG-FP3 is shown below.

Table 6-3. Example of Settings for PG-FP3

Communication Mode	Example of Setting for PG-F	FP3	Number of VPP Pulses Note 1
3-wire serial I/O	COMM PORT	SIO-ch0/1/2	0/1/2
	CPU CLK	On Target Board	
		In Flashpro	
	On Target Board	4.1943 MHz	
	SIO CLK	1.0 MHz	
	In Flashpro	4.0 MHz	
	SIO CLK	1.0 MHz	
UART	COMM PORT	UART-ch0/1	8/9
	CPU CLK	On Target Board	
	On Target Board	4.1943 MHz	
	UART BPS	9600 bps <sup>Note 2</sup>	
Pseudo 3-wire	COMM PORT	PortA	12
	CPU CLK	On Target Board	
		In Flashpro	
	On Target Board	4.1943 MHz	
	SIO CLK	1.0 kHz	
	In Flashpro	4.0 MHz	
	SIO CLK	1.0 kHz	

**Notes 1.** The number of VPP pulses supplied from Flashpro III when serial communication is initialized. The pins to be used for communication are determined according to the number of these pulses.

2. Select one of 9600 bps, 19200 bps, 38400 bps, or 768000 bps.

Remark COMM PORT: Selection of serial port

SIO CLK : Selection of serial clock frequency

CPU CLK : Selection of source of CPU clock to be input



#### **★** 7. ELECTRICAL SPECIFICATIONS

#### Absolute Maximum Ratings ( $T_A = 25^{\circ}C$ )

Parameter	Symbol		Conditions		Ratings	Unit
Supply voltage	V <sub>DD</sub>				-0.3 to +6.5	V
	V <sub>PP</sub>				-0.3 to +10.5	V
Supply voltage   Vod   Vod   -0.3 to +6.5     Vod   AVREF0   -0.3 to +0.5     AVREF0   AVREF0   -0.3 to Vod +0.     AVREF1   -0.3 to Vod +0.     AVS   -0.3 to Vod +0.     AVS   -0.3 to Vod +0.     P00-P05, P07, P10-P17, P20-P27, P30-P37, P40-P47, P50-P57, P60-P67, P70-P72, P120-P127, P130, P131, X1, X2, XT2, RESET   -0.3 to Vod +0.     Analog input voltage   Vod   -0.3 to Vod +0.     Avs - 0.3 to Vod +0.     Avs - 0.40 -     Avs - 0.3 to Vod +0.     Avs - 0.3 to Vod +0.     Avs - 0.40 -     Avs - 0.50	-0.3 to V <sub>DD</sub> + 0.3	V				
	AV <sub>REF1</sub>		-0.3 to +6.5  -0.3 to +10.5  -0.3 to V <sub>DD</sub> + 0.3  -10  nor P01-P05, P30-P37, P60-P67, P60-P67, P60-P67, P60-P67, P60-P67, P60-P65, P60-P63  -0.3 to V <sub>DD</sub> + 0.3  -10  nor P01-P05, P30-P37, P60-P67, P60-P67, P60-P67, P60-P67, P60-P67, P60-P67, P60-P65, P	V		
	AVss				-0.3 to +0.3	V
Input voltage	VII	P50-P57, P64-P67, P70-P72, P120-P127, P130, P131,			-0.3 to V <sub>DD</sub> + 0.3	V
	Vı2	P60-P63	N-ch open drain		-0.3 to +16	V
Output voltage	Vo		1		-0.3 to V <sub>DD</sub> + 0.3	V
Analog input voltage	Van	P10-P17	Analog input pin		AVss - 0.3 to AVREF0 + 0.3	V
Output	Іон	Per pin			AVss - 0.3 to AVREF0 + 0.3 -10 -15 -15	mA
current, high			5, P30-P37, P56, P	57, P60-P67,	-15	mA
				7, P50-P55,	-15	mA
Output	<sub>OL</sub> Note	Per pin	Per pin Peak value		30	mA
current, low				rms value	15	mA
		Total for P50-P55	i	Peak value	100	mA
				rms value	70	mA
		Total for P56, P5	7, P60-P63	Peak value	100	mA
				rms value	70	mA
		Total for P10-P17	, P20-P27,	Peak value	50	mA
		P40-P47, P70-P7	2, P130, P131	rms value	20	mA
		Total for P01-P05	i, P30-P37,	Peak value	-0.3 to Vdd + 0.3  -0.3 to +16  -0.3 to Vdd + 0.3  AVss - 0.3 to AVrefo + 0.3  -10  -15  -15  30  15  100  70  100  70  50  20  50  20  -40 to +85	mA
		P64-P67, P120-P	127	rms value	20	mA
Operating ambient	TA	During normal op	eration		-40 to +85	°C
temperature		During flash mem	nory programming		10 to 40	°C
Storage temperature	T <sub>stg</sub>				-65 to +125	°C

**Note** The rms value should be calculated as follows: [rms value] = [Peak value]  $\times \sqrt{\text{Duty}}$ 

Caution Product quality may suffer if the absolute maximum rating is exceeded even momentarily for any parameter. That is, the absolute maximum ratings are rated values at which the product is on the verge of suffering physical damage, and therefore the product must be used under conditions that ensure that the absolute maximum ratings are not exceeded.



Main System Clock Oscillator Characteristics (T<sub>A</sub> = −40 to +85°C, V<sub>DD</sub> = 2.7 to 5.5 V)

Resonator	Recommended Circuit	Parameter	Conditions	MIN.	TYP.	MAX.	Unit
Ceramic resonator	X2 X1 VPP	Oscillation frequency (fx) <sup>Note 1</sup>	V <sub>DD</sub> = Oscillation voltage range	1.0		5.0	MHz
	+	Oscillation stabilization time Note 2	After V <sub>DD</sub> reaches oscillation voltage range MIN.			4	ms
Crystal resonator	X2 X1 VPP	Oscillation frequency (fx) <sup>Note 1</sup>		1.0		5.0	MHz
	+	Oscillation	V <sub>DD</sub> = 4.5 to 5.5 V			10	ms
	702 401	stabilization time <sup>Note 2</sup>				5.0	
External clock	X2 X1	X1 input frequency (fx)Note 1		1.0		5.0	MHz
	μPD74HCU04	X1 input high-/low-level width (txH, txL)		85		500	ns

- Notes 1. Indicates only oscillator characteristics. Refer to AC Characteristics for instruction execution time.
  - 2. Time required to stabilize oscillation after reset or STOP mode release.
- Cautions 1. When using the main system clock oscillator, wire as follows in the area enclosed by the broken lines in the above figures to avoid an adverse effect from wiring capacitance.
  - · Keep the wiring length as short as possible.
  - · Do not cross the wiring with the other signal lines.
  - . Do not route the wiring near a signal line through which a high fluctuating current flows.
  - Always make the ground point of the oscillator capacitor the same potential as Vss1.
  - . Do not ground the capacitor to a ground pattern through which a high current flows.
  - Do not fetch signals from the oscillator.
  - 2. When the main system clock is stopped and the system is operating on the subsystem clock, wait until the oscillation stabilization time has been secured by the program before switching back to the main system clock.

**Remark** For the resonator selection and oscillator constant, customers are requested to either evaluate the oscillation themselves or apply to the resonator manufacturer for evaluation.

Resonator	Recommended Circuit	Parameter	Conditions	MIN.	TYP.	MAX.	Unit
Crystal resonator	VPP XT2 XT1	Oscillation frequency (fxt)Note 1		32	32.768	35	kHz
	C4= C3 =	Oscillation	V <sub>DD</sub> = 4.5 to 5.5 V		1.2	2	s
	<i>m</i>	stabilization timeNote 2				10	
External	XT2 XT1	XT1 input		32		100	kHz
clock		frequency (fxt)Note 1					
	μPD74HCU04	XT1 input high-/low-level width (txth, txtl)		5		15	μs

- Notes 1. Indicates only oscillator characteristics. Refer to AC Characteristics for instruction execution time.
  - 2. Time required to stabilize oscillation after VDD reaches oscillation voltage range MIN.

# Cautions 1. When using the subsystem clock oscillator, wire as follows in the area enclosed by the broken lines in the above figures to avoid an adverse effect from wiring capacitance.

- · Keep the wiring length as short as possible.
- · Do not cross the wiring with the other signal lines.
- Do not route the wiring near a signal line through which a high fluctuating current flows.
- . Always make the ground point of the oscillator capacitor the same potential as Vss1.
- . Do not ground the capacitor to a ground pattern through which a high current flows.
- · Do not fetch signals from the oscillator.
- The subsystem clock oscillator is designed as a low-amplitude circuit for reducing current consumption, and is more prone to malfunction due to noise than the main system clock oscillator. Particular care is therefore required with the wiring method when the subsystem clock is used.

**Remark** For the resonator selection and oscillator constant, customers are requested to either evaluate the oscillation themselves or apply to the resonator manufacturer for evaluation.

#### Capacitance (TA = 25°C, VDD = Vss = 0 V)

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input capacitance	Cin	f = 1 MHz Unmeasured pins returned to	0 V.			15	pF
I/O capacitance	Сю	f = 1 MHz Unmeasured pins returned to 0 V.	P01-P05, P10-P17, P20-P27, P30-P37, P40-P47, P50-P57, P64-P67, P70-P72, P120-P127, P130, P131			15	pF
			P60-P63			20	pF

**Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of port pins.



### DC Characteristics ( $T_A = -40 \text{ to } +85^{\circ}\text{C}$ , $V_{DD} = 2.7 \text{ to } 5.5 \text{ V}$ )

Parameter	Symbol	Conditions		MIN.	TYP.	MAX.	Unit
Input voltage, high	V <sub>IH1</sub>	P10-P17, P21, P23, P30-P32, P35-P37, P40-P47, P50-P57, P64-P67, P71, P120-P127, P130, P131	V <sub>DD</sub> = 2.7 to 5.5 V	0.7V <sub>DD</sub>		V <sub>DD</sub>	V
	V <sub>IH2</sub>	P00-P05, P20, P22, P24-P27, P33, P34, P70, P72, RESET	V <sub>DD</sub> = 2.7 to 5.5 V	0.8V <sub>DD</sub>		V <sub>DD</sub>	V
	VIH3	P60-P63 (N-ch open drain)	V <sub>DD</sub> = 2.7 to 5.5 V	0.7V <sub>DD</sub>		15	V
	V <sub>IH4</sub>	X1, X2	V <sub>DD</sub> = 2.7 to 5.5 V	V <sub>DD</sub> - 0.5		V <sub>DD</sub>	V
	V <sub>IH5</sub>	XT1/P07, XT2	4.5 V ≤ V <sub>DD</sub> ≤ 5.5 V	0.8V <sub>DD</sub>		V <sub>DD</sub>	V
			2.7 V ≤ V <sub>DD</sub> < 4.5 V	0.9V <sub>DD</sub>		V <sub>DD</sub>	V
Input voltage, low	VIL1	P10-P17, P21, P23, P30-P32, P35-P37, P40-P47, P50-P57, P64-P67, P71, P120-P127, P130, P131	V <sub>DD</sub> = 2.7 to 5.5 V	0		0.3V <sub>DD</sub>	V
	VIL2	P00-P05, P20, P22, P24-P27, P33, P34, P70, P72, RESET	V <sub>DD</sub> = 2.7 to 5.5 V	0		0.2V <sub>DD</sub>	V
	VIL3	P60-P63	4.5 V ≤ V <sub>DD</sub> ≤ 5.5 V	0		0.3V <sub>DD</sub>	V
			2.7 V ≤ V <sub>DD</sub> < 4.5 V	0		0.2V <sub>DD</sub>	V
	VIL4	X1, X2	V <sub>DD</sub> = 2.7 to 5.5 V	0		0.4	V
	VIL5	XT1/P07, XT2	4.5 V ≤ V <sub>DD</sub> ≤ 5.5 V	0		0.2V <sub>DD</sub>	V
			$2.7 \text{ V} \leq \text{V}_{DD} < 4.5 \text{ V}$	0		0.1V <sub>DD</sub>	V
Output voltage,	Vон	$V_{DD} = 4.5 \text{ to } 5.5 \text{ V}, \text{ IoH} = -1 \text{ mA}$		V <sub>DD</sub> - 1.0			V
high		Iон = −100 μA		V <sub>DD</sub> - 0.5			V
Output voltage, low	Vol1	P50-P57, P60-P63	$V_{DD} = 4.5 \text{ to } 5.5 \text{ V},$ $I_{OL} = 15 \text{ mA}$		0.4	2.0	V
		P01-P05, P10-P17, P20-P27, P30-P37, P40-P47, P64-P67, P70-P72, P120-P127, P130, P131	V <sub>DD</sub> = 4.5 to 5.5 V, I <sub>OL</sub> = 1.6 mA			0.4	V
	V <sub>OL2</sub>	SB0, SB1, SCK0	$V_{DD} = 4.5 \text{ to } 5.5 \text{ V},$ open drain, pulled-up (R = 1 k $\Omega$ )			0.2V <sub>DD</sub>	V
	V <sub>OL3</sub>	IoL = 400 μA				0.5	V

**Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of port pins.



## DC Characteristics (T<sub>A</sub> = -40 to +85°C, V<sub>DD</sub> = 2.7 to 5.5 V)

Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Input leakage current, high	Ішні	VIN = VDD	P00-P05, P10-P17, P20-P27, P30-P37, P40-P47, P50-P57, P60-P67, P70-P72, P120-P127, P130, P131, RESET			3	μΑ
	I <sub>LIH2</sub>		X1, X2, XT1/P07, XT2			20	μΑ
	Ілнз	Vin = 15 V	P60 to P63			80	μΑ
Input leakage current, low	ILIL1	Vin = 0 V	P00-P05, P10-P17, P20-P27, P30-P37, P40-P47, P50-P57, P64-P67, P70-P72, P120-P127, P130, P131, RESET			-3	μΑ
	I <sub>LIL2</sub>		X1, X2, XT1/P07, XT2			-20	μΑ
	ILIL3		P60-P63			_3Note 1	μΑ
Output leakage current, high	Ісон	Vout = Vdd				3	μΑ
Output leakage current, low	ILOL	Vout = 0 V				-3	μΑ
Software pull-up resistor Note 2	R		-P05, P10-P17, P20-P27, P30-P37, P57, P64-P67, P70-P72, P120-P127,	15	30	90	kΩ

**Notes 1.** A low-level input leakage current of  $-200~\mu\text{A}$  (MAX.) flows only for 1.5 clocks (without wait) after a read instruction has been executed to port 6 (P6) or port mode register 6 (PM6). At times other than this 1.5-clock interval, a  $-3~\mu\text{A}$  (MAX.) current flows.

**2.** Software pull-up resistor can only be used within the range  $V_{DD}$  = 2.7 to 5.5 V.

**Remark** Unless specified otherwise, the characteristics of alternate-function pins are the same as those of port pins.



### DC Characteristics (T<sub>A</sub> = -40 to +85°C, V<sub>DD</sub> = 2.7 to 5.5 V)

Parameter	Symbol	Conditio	MIN.	TYP.	MAX.	Unit	
Power supply current Note 5	I <sub>DD1</sub> Note 5	5.0 MHz crystal oscillation operating mode	V <sub>DD</sub> = 5.0 V ±10% <sup>Note 1</sup>		6.2	12.5	mA
		(fxx = 2.5 MHz) <sup>Note 3</sup> 5.0 MHz crystal oscillation operating mode (fxx = 5.0 MHz) <sup>Note 4</sup>	V <sub>DD</sub> = 3.0 V ±10% <sup>Note 2</sup>		1.3	3.1	mA
			V <sub>DD</sub> = 5.0 V ±10% <sup>Note 1</sup>		13.1	25.7	mA
			$V_{DD} = 3.0 \text{ V} \pm 10\%^{\text{Note 2}}$		2.1	4.9	mA
	I <sub>DD2</sub>	5.0 MHz crystal oscillation HALT mode (fxx = 2.5 MHz) <sup>Note 3</sup>	V <sub>DD</sub> = 5.0 V ±10%				
			Peripheral functions operating			5.6	mA
			Peripheral functions not operating		1.0	2.8	mA
			V <sub>DD</sub> = 3.0 V ±10%				
			Peripheral functions operating			2.9	mA
			Peripheral functions not operating		0.44	1.1	mA
		5.0 MHz crystal oscillation HALT mode (fxx = 5.0 MHz)Note 4	V <sub>DD</sub> = 5.0 V ±10%				
1			Peripheral functions operating			8.4	mA
			Peripheral functions not operating		1.3	3.1	mA
			V <sub>DD</sub> = 3.0 V ±10%				
			Peripheral functions operating			4.5	mA
			Peripheral functions not operating		0.6	1.5	mA
	I <sub>DD3</sub> Note 5	32.768 kHz crystal oscillation operating mode <sup>Note 6</sup>	V <sub>DD</sub> = 5.0 V ±10%		110	220	μΑ
			V <sub>DD</sub> = 3.0 V ±10%		86	172	μΑ
	I <sub>DD4</sub> Note 5		V <sub>DD</sub> = 5.0 V ±10%		22.5	45	μΑ
		HALT mode <sup>Note 6</sup>	V <sub>DD</sub> = 3.0 V ±10%		3.2	6.4	μΑ
	<sub>DD5</sub> Note 5	XT1 = V <sub>DD</sub> STOP mode When feedback resistor is used	V <sub>DD</sub> = 5.0 V ±10%		1.0	30	μΑ
			V <sub>DD</sub> = 3.0 V ±10%		0.5	10	μΑ
	I <sub>DD6</sub> Note 5	XT1 = V <sub>DD</sub>	V <sub>DD</sub> = 5.0 V ±10%		0.1	30	μΑ
		STOP mode When feedback resistor is not used	V <sub>DD</sub> = 3.0 V ±10%		0.05	10	μΑ

Notes 1. High-speed mode operation (when the processor clock control register (PCC) is set to 00H).

- 2. Low-speed mode operation (when PCC is set to 04H).
- 3. Operation with main system clock fxx = fx/2 (when the oscillation mode select register (OSMS) is set to 00H)
- **4.** Operation with main system clock fxx = fx (when OSMS is set to 01H)
- **5.** Refers to the current flowing to the V<sub>DD0</sub> and V<sub>DD1</sub> pins. The current flowing to the A/D converter, D/A converter, and on-chip pull-up resistor is not included.
- **6.** When the main system clock operation is stopped.



#### **AC Characteristics**

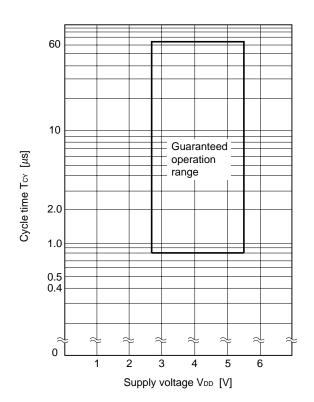
#### (1) Basic operation (T<sub>A</sub> = -40 to +85°C, V<sub>DD</sub> = 2.7 to 5.5 V)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit	
Cycle time (Min. instruction	Тсү	Operating with main system clock (fxx = 2.5 MHz)Note 1	V <sub>DD</sub> = 2.7 to 5.5 V	0.8		64	μs
execution time)		Operating with main system	$3.5 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	0.4		32	μs
		clock (fxx = 5.0 MHz)Note 2	2.7 V ≤ V <sub>DD</sub> < 3.5 V	0.8		32	μs
		Operating with subsystem clock	40Note 3	122	125	μs	
TI00 input high-/	<b>t</b> TIH00	3.5 V ≤ V <sub>DD</sub> ≤ 5.5 V	2/f <sub>sam</sub> + 0.1 <sup>Note 4</sup>			μs	
low-level width	<b>t</b> TIL00	2.7 V ≤ V <sub>DD</sub> < 3.5 V	2/f <sub>sam</sub> + 0.2 <sup>Note 4</sup>			μs	
TI01 input high-/	<b>t</b> TIH01	V <sub>DD</sub> = 2.7 to 5.5 V		10			μs
low-level width	<b>t</b> TIL01						
TI1, TI2 input	f <sub>Tl1</sub>	V <sub>DD</sub> = 4.5 to 5.5 V	0		4	MHz	
frequency				0		275	kHz
TI1, TI2 input	<b>t</b> тін1	V <sub>DD</sub> = 4.5 to 5.5 V	100			ns	
high-/low-level width	tTIL1			1.8			μs
Interrupt request	tinth	INTP0	$3.5 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	2/f <sub>sam</sub> + 0.1 Note 4			μs
input high-/	tintl		2.7 V ≤ V <sub>DD</sub> < 3.5 V	2/f <sub>sam</sub> + 0.2 <sup>Note 4</sup>			μs
low-level width		INTP1-INTP5, P40-P47	V <sub>DD</sub> = 2.7 to 5.5 V	10			μs
RESET low- level width	trsl	V <sub>DD</sub> = 2.7 to 5.5 V		10			μs

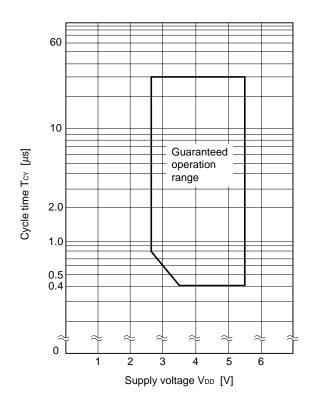
**Notes 1.** Operation with main system clock fxx = fx/2 (when the oscillation mode select register (OSMS) is set to 00H)

- **2.** Operation with main system clock fxx = fx (when OSMS is set to 01H)
- 3. Value when external clock is used. When a crystal resonator is used, it is 114  $\mu$ s (MIN.)
- **4.** Selection of  $f_{sam} = f_{xx}/2^N$ ,  $f_{xx}/32$ ,  $f_{xx}/64$ , and  $f_{xx}/128$  is possible with bits 0 and 1 (SCS0, SCS1) of the sampling clock select register (SCS) (when N= 0 to 4).

Tcy vs.  $V_{DD}$  (@fxx = fx/2 main system clock operation)



Tcy vs.  $V_{DD}$  (@fxx = fx main system clock operation)





#### (2) Read/write operation

### (a) When MCS = 1, PCC2 to PCC0 = 000B ( $T_A = -40 \text{ to } +85^{\circ}\text{C}$ , $V_{DD} = 3.5 \text{ to } 5.5 \text{ V}$ )

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
ASTB high-level width	tasth		0.85tcy - 50		ns
Address setup time	tads		0.85tcy - 50		ns
Address hold time	tadh		50		ns
Data input time from address	tADD1			(2.85 + 2n)tcy - 80	ns
	tADD2			(4 + 2n)tcy - 100	ns
Data input time from $\overline{RD} \downarrow$	trdd1			(2 + 2n)tcy - 100	ns
	trdd2			(2.85 + 2n)tcy - 100	ns
Read data hold time	trdh		0		ns
RD low-level width	trdL1		(2 + 2n)tcy - 60		ns
	trdl2		(2.85 + 2n)tcy - 60		ns
$\overline{\text{WAIT}} \downarrow \text{ input time from } \overline{\text{RD}} \downarrow$	trdwt1			0.85tcy - 50	ns
	trdwt2			2tcy - 60	ns
$\overline{\mathrm{WAIT}}{\downarrow}$ input time from $\overline{\mathrm{WR}}{\downarrow}$	twrwt			2tcy - 60	ns
WAIT low-level width	twTL		(1.15 + 2n)tcy	(2 + 2n)tcy	ns
Write data setup time	twos		(2.85 + 2n)tcy - 100		ns
Write data hold time	twdh		20		ns
WR low-level width	twrL		(2.85 + 2n)tcy - 60		ns
$\overline{\text{RD}} \downarrow \text{ delay time from ASTB} \downarrow$	tastrd		25		ns
$\overline{\mathrm{WR}} \!\!\downarrow \mathrm{delay}$ time from ASTB $\!\!\downarrow$	tastwr		0.85tcy + 20		ns
ASTB↑ delay time from RD↑ at external fetch	<b>t</b> rdast		0.85tcy - 10	1.15tcy + 20	ns
Address hold time from RD↑ at external fetch	<b>t</b> RDADH		0.85tcy - 50	1.15tcy + 50	ns
Write data output time from RD↑	trowd		40		ns
Write data output time from $\overline{\text{WR}} \downarrow$	twrwd		0	50	ns
Address hold time from $\overline{\mathrm{WR}} \!\!\uparrow$	twradh		0.85tcy	1.15tcy + 40	ns
RD↑ delay time from WAIT↑	twtrd		1.15tcy + 40	3.15tcy + 40	ns
WR↑ delay time from WAIT↑	twrwr		1.15tcy + 30	3.15tcy + 30	ns

- Remarks 1. MCS: Bit 0 of the oscillation mode select register (OSMS)
  - 2. PCC2 to PCC0: Bits 2 to 0 of the processor clock control register (PCC)
  - 3. tcy = Tcy/4
  - 4. n indicates the number of waits.



#### (b) When MCS = 0 or PCC2 to PCC0 $\neq$ 000B (TA = -40 to +85°C, VDD = 2.7 to 5.5 V)

Parameter	Symbol	Conditions	MIN.	MAX.	Unit
ASTB high-level width	<b>t</b> asth		tcy - 80		ns
Address setup time	tADS		tcy - 80		ns
Address hold time	tadh		0.4tcy - 10		ns
Data input time from address	tADD1			(3 + 2n)tcy - 160	ns
	tADD2			(4 + 2n)tcy - 200	ns
Data input time from RD↓	tRDD1			(1.4 + 2n)tcy - 70	ns
	tRDD2			(2.4 + 2n)tcy - 70	ns
Read data hold time	<b>t</b> RDH		0		ns
RD low-level width	tRDL1		(1.4 + 2n)tcy - 20		ns
	tRDL2		(2.4 + 2n)tcy - 20		ns
WAIT↓ input time from RD↓	<b>t</b> RDWT1			tcy - 100	ns
	trdwt2			2tcy - 100	ns
WAIT↓ input time from WR↓	twrwt			2tcy - 100	ns
WAIT low-level width	twtL		(1 + 2n)tcy	(2 + 2n)tcy	ns
Write data setup time	twos		(2.4 + 2n)tcy - 60		ns
Write data hold time	twdH		20		ns
WR low-level width	twrL		(2.4 + 2n)tcy - 20		ns
RD↓ delay time from ASTB↓	tastrd		0.4tcy - 30		ns
WR↓ delay time from ASTB↓	tastwr		1.4tcy - 30		ns
ASTB↑ delay time from RD↑ at external fetch	trdast		tcy - 10	tcy + 20	ns
Address hold time from RD↑ at external fetch	trdadh		tcy - 50	tey + 50	ns
Write data output time from RD↑	trdwd		0.4tcy - 20		ns
Write data output time from WR↓	twrwd		0	60	ns
Address hold time from WR↑	twradh		tcy	tcy + 60	ns
RD↑ delay time from WAIT↑	twtrd		0.6tcy + 180	2.6tcy + 180	ns
WR↑ delay time from WAIT↑	twrwr		0.6tcy + 120	2.6tcy + 120	ns

- Remarks 1. MCS: Bit 0 of the oscillation mode select register (OSMS)
  - 2. PCC2 to PCC0: Bits 2 to 0 of the processor clock control register (PCC)
  - 3. tcy = Tcy/4
  - 4. n indicates the number of waits.



### (3) Serial interface (T<sub>A</sub> = -40 to +85°C, V<sub>DD</sub> = 2.7 to 5.5 V)

#### (a) Serial interface channel 0

# (i) 3-wire serial I/O mode (SCK0... Internal clock output)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
SCK0 cycle time	tkcy1	4.5 V ≤ V <sub>DD</sub> ≤ 5.5 V	800			ns
	,	2.7 V ≤ V <sub>DD</sub> < 4.5 V	1,600			ns
SCK0 high-/low-level	tkH1, tkL1	V <sub>DD</sub> = 4.5 to 5.5 V	tkcy1/2 - 50			ns
width			tkcy1/2 - 100			ns
SI0 setup time	tsık1	4.5 V ≤ V <sub>DD</sub> ≤ 5.5 V	100			ns
(to SCK0↑)		$2.7 \text{ V} \leq \text{V}_{DD} < 4.5 \text{ V}$	150			ns
SI0 hold time (from SCK0↑)	tksi1		400			ns
SO0 output delay time from SCK0↓	tkso1	C = 100 pF <sup>Note</sup>			300	ns

**Note** C is the load capacitance of the  $\overline{SCK0}$  and SO0 output lines.

## (ii) 3-wire serial I/O mode (SCK0... External clock input)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
SCK0 cycle time	tkcy2	4.5 V ≤ V <sub>DD</sub> ≤ 5.5 V	800			ns
		$2.7 \text{ V} \leq \text{V}_{DD} < 4.5 \text{ V}$	1,600			ns
SCK0 high-/low-level	tкн2, tкL2	4.5 V ≤ V <sub>DD</sub> ≤ 5.5 V	400			ns
width		2.7 V ≤ V <sub>DD</sub> < 4.5 V	800			ns
SI0 setup time (to SCK0↑)	tsıк2	2.7 V ≤ V <sub>DD</sub> ≤ 5.5 V	100			ns
SI0 hold time (from SCK0↑)	tĸsı2		400			ns
SO0 output delay time from SCK0↓	tkso2	C = 100 pF <sup>Note</sup>			300	ns
SCK0 rise/fall time	tr2, tr2	When using external device expansion function			160	ns
		When not using external device expansion function			1,000	ns

Note C is the load capacitance of the SO0 output line.



# (iii) 2-wire serial I/O mode (SCK0... Internal clock output)

Parameter	Symbol	Co	nditions	MIN.	TYP.	MAX.	Unit
SCK0 cycle time	tксүз	$R = 1 k\Omega$ ,	$2.7 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	1,600			ns
SCK0 high-level width	tкнз	C = 100 pF <sup>Note</sup>	V <sub>DD</sub> = 2.7 to 5.5 V	tксүз/2 – 160			ns
SCK0 low-level width	tкLз		V <sub>DD</sub> = 4.5 to 5.5 V	tксүз/2 — 50			ns
				tксүз/2 – 100			ns
SB0, SB1 setup time	tsıкз		$4.5 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	300			ns
(to SCK0↑)			2.7 V ≤ V <sub>DD</sub> < 4.5 V	350			ns
SB0, SB1 hold time (from SCK0↑)	tksi3			600			ns
SB0, SB1 output delay time from SCK0↓	tкsоз			0		300	ns

**Note** R and C are the load resistance and load capacitance of the  $\overline{SCK0}$ , SB0, and SB1 output lines.

# (iv) 2-wire serial I/O mode (SCK0... External clock input)

Parameter	Symbol	Со	nditions	MIN.	TYP.	MAX.	Unit
SCK0 cycle time	tkcy4	2.7 V ≤ V <sub>DD</sub> ≤ 5	5.5 V	1,600			ns
SCK0 high-level width	t <sub>KH4</sub>	2.7 V ≤ V <sub>DD</sub> ≤ 5	i.5 V	650			ns
SCK0 low-level width	t <sub>KL4</sub>	2.7 V ≤ V <sub>DD</sub> ≤ 5	5.5 V	800			ns
SB0, SB1 setup time (to SCK0↑)	tsık4	$V_{DD} = 2.7 \text{ to } 5.5$	5 V	100			ns
SB0, SB1 hold time (from SCK0↑)	tksi4			tkcy4/2			ns
SB0, SB1 output delay	<b>t</b> ks04	$R = 1 k\Omega$ ,	$4.5~\textrm{V} \leq \textrm{V}_\textrm{DD} \leq 5.5~\textrm{V}$	0		300	ns
time from SCK0↓		C = 100 pF <sup>Note</sup>	$2.7 \text{ V} \le \text{V}_{DD} < 4.5 \text{ V}$	0		500	ns
SCK0 rise/fall time	tr4, tf4	When using ex expansion fund				160	ns
		When not using expansion fund	g external device			1,000	ns

Note R and C are the load resistance and load capacitance of the SB0 and SB1 output lines.



# (v) SBI mode ( $\overline{\text{SCK0}}$ ... Internal clock output) ( $\mu$ PD78F0058 only)

Parameter	Symbol	Cor	nditions	MIN.	TYP.	MAX.	Unit
SCK0 cycle time	tkcy5	$4.5 \text{ V} \leq \text{V}_{DD} \leq 5$	.5 V	800			ns
		2.7 V ≤ V <sub>DD</sub> < 4	.5 V	3,200			ns
SCK0 high-/low-level	tkH5, tkL5	4.5 V ≤ V <sub>DD</sub> ≤ 5	.5 V	tkcy5/2 - 50			ns
width		2.7 V ≤ V <sub>DD</sub> < 4	.5 V	tксү5/2 – 150			ns
SB0, SB1 setup time	tsik5	4.5 V ≤ V <sub>DD</sub> ≤ 5	.5 V	100			ns
(to SCK0↑)		2.7 V ≤ V <sub>DD</sub> < 4	.5 V	300			ns
SB0, SB1 hold time (from SCK0↑)	tksi5			tксү5/2			ns
SB0, SB1 output delay	tkso5	$R = 1 k\Omega$ ,	V <sub>DD</sub> = 4.5 to 5.5 V	0		250	ns
time from SCK0↓		C = 100 pF <sup>Note</sup>		0		1,000	ns
SB0, SB1↓ from SCK0↑	tкsв			tkcy5			ns
SCK0↓ from SB0, SB1↓	tsвк			tkcy5			ns
SB0, SB1 high-level width	tsвн			tkcy5			ns
SB0, SB1 low-level width	tsbl			tkcy5			ns

**Note** R and C are the load resistance and load capacitance of the SCKO, SBO, and SB1 output lines.

### (vi) SBI mode (SCK0... External clock input) (μPD78F0058 only)

Parameter	Symbol	Cor	nditions	MIN.	TYP.	MAX.	Unit
SCK0 cycle time	<b>t</b> ксу6	$4.5 \text{ V} \leq \text{V}_{DD} \leq 5$	.5 V	800			ns
		$2.7 \text{ V} \leq \text{V}_{DD} < 4$	.5 V	3,200			ns
SCK0 high-/low-level	tкн6, tкL6	$4.5 \text{ V} \leq \text{V}_{\text{DD}} \leq 5$	.5 V	400			ns
width		$2.7 \text{ V} \leq \text{V}_{DD} < 4$	.5 V	1,600			ns
SB0, SB1 setup time	tsik6	$4.5 \text{ V} \leq \text{V}_{\text{DD}} \leq 5$	4.5 V ≤ V <sub>DD</sub> ≤ 5.5 V				ns
(to <del>SCK0</del> ↑)		$2.7 \text{ V} \leq \text{V}_{DD} < 4$	.7 V ≤ VDD < 4.5 V				ns
SB0, SB1 hold time (from SCK0↑)	tksi6			tксү6/2			ns
SB0, SB1 output delay	tkso6	$R = 1 k\Omega$ ,	V <sub>DD</sub> = 4.5 to 5.5 V	0		300	ns
time from SCK0↓		C = 100 pF <sup>Note</sup>		0		1,000	ns
SB0, SB1↓ from SCK0↑	tksb			tkcy6			ns
SCK0↓ from SB0, SB1↓	tsвк			tkcy6			ns
SB0, SB1 high-level width	tsвн			tkcy6			ns
SB0, SB1 low-level width	tsbl			tkcy6			ns
SCK0 rise/fall time	tre, tre	_	When using external device expansion function			160	ns
		When not using expansion func	g external device tion			1,000	ns

Note R and C are the load resistance and load capacitance of the SB0 and SB1 output lines.



### (vii) I<sup>2</sup>C bus mode (SCL... Internal clock output) ( $\mu$ PD78F0058Y only)

Parameter	Symbol	Со	nditions	MIN.	TYP.	MAX.	Unit
SCL cycle time	<b>t</b> ксү7	$R = 1 k\Omega$ ,	$2.7 \text{ V} \leq \text{V}_{DD} < 5.5 \text{ V}$	10			μs
SCL high-level width	<b>t</b> кн7	C = 100 pF <sup>Note</sup>	2.7 V ≤ V <sub>DD</sub> < 5.5 V	tксү7 – 160			μs
SCL low-level width	t <sub>KL7</sub>		4.5 V ≤ V <sub>DD</sub> < 5.5 V	tксү7 — 50			ns
			2.7 V ≤ V <sub>DD</sub> < 4.5 V	tксү7 — 100			ns
SDA0, SDA1 setup time	tsıк7		$2.7 \text{ V} \leq \text{V}_{DD} < 5.5 \text{ V}$	200			ns
(to SCL↑)							
SDA0, SDA1 hold time	tksi7			0			ns
(from SCL↓)							
SDA0, SDA1 output delay	<b>t</b> кso7		4.5 V ≤ V <sub>DD</sub> < 5.5 V	0		300	ns
time from SCL↓				0		500	ns
SDA0, SDA1↓ from SCL↑				200			ns
or SDA0, SDA1↑ from SCL↑							
SCL↓ from SDA0, SDA1↓	tsвк			400			ns
SDA0, SDA1 high-level width	tsвн			500			ns

**Note** R and C are the load resistance and load capacitance of the SCL, SDA0, and SDA1 output lines.

### (viii) I<sup>2</sup>C bus mode (SCL... External clock input) (µPD78F0058Y only)

Parameter	Symbol	Со	nditions	MIN.	TYP.	MAX.	Unit
SCL cycle time	<b>t</b> ксү8			1			μs
SCL high-level width	<b>t</b> кн8			400			ns
SDA0, SDA1 setup time (to SCL <sup>↑</sup> )	tsik8			200			ns
SDA0, SDA1 hold time (from SCL↓)	tksi8			0			ns
SDA0, SDA1 output delay	tkso8	$R = 1 k\Omega$ ,	4.5 V ≤ V <sub>DD</sub> < 5.5 V	0		300	ns
time from SCL↓		C = 100 pFNote		0		500	ns
SDA0, SDA1↓ from SCL↑ or SDA0, SDA1↑ from SCL↑				200			ns
SCL↓ from SDA0, SDA1↓	<b>t</b> sbk			400			ns
SDA0, SDA1 high-level width	tsвн			500			ns

**Note** R and C are the load resistance and load capacitance of the SDA0 and SDA1 output lines.

### (b) Serial interface channel 1

# (i) 3-wire serial I/O mode (SCK1...Internal clock output)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
SCK1 cycle time	tkcy9	$4.5 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	800			ns
		$2.7 \text{ V} \leq \text{V}_{DD} < 4.5 \text{ V}$	1,600			ns
SCK1 high-/low-level width	tkH9, tkL9	V <sub>DD</sub> = 4.5 to 5.5 V	tксү9/2 - 50			ns
			tксү9/2 – 100			ns
SI1 setup time (to SCK1↑)	tsik9	$4.5~\textrm{V} \leq \textrm{V}_\textrm{DD} \leq 5.5~\textrm{V}$	100			ns
		$2.7 \text{ V} \leq \text{V}_{DD} < 4.5 \text{ V}$	150			ns
SI1 hold time (from SCK1↑)	tksi9		400			ns
SO1 output delay time from $\overline{\text{SCK1}} \downarrow$	<b>t</b> KSO9	C = 100 pF <sup>Note</sup>			300	ns

**Note** C is the load capacitance of the  $\overline{SCK1}$  and SO1 output lines.

### (ii) 3-wire serial I/O mode (SCK1...External clock input)

Parameter	Symbol	Cor	nditions	MIN.	TYP.	MAX.	Unit
SCK1 cycle time	<b>t</b> KCY10	$4.5 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$		800			ns
		2.7 V ≤ V <sub>DD</sub> < 4.5 V		1,600			ns
SCK1 high-/low-level width	tkH10, tkL10	4.5 V ≤ V <sub>DD</sub> ≤ 5.5 V		400			ns
		2.7 V ≤ V <sub>DD</sub> < 4.5 V		800			ns
SI1 setup time (to SCK1↑)	tsik10	V <sub>DD</sub> = 2.7 to 5.5 V		100			ns
SI1 hold time (from SCK1↑)	tkis10			400			ns
SO1 output delay time from SCK1↓	<b>t</b> KSO10	C = 100 pF <sup>Note</sup>	V <sub>DD</sub> = 2.7 to 5.5 V			300	ns
SCK1 rise/fall time	t <sub>R10</sub> , t <sub>F10</sub>	When using external device expansion function				160	ns
		When not using expansion function				1,000	ns

Note C is the load capacitance of the SO1 output line.



# (iii) 3-wire serial I/O mode with automatic transmit/receive function (SCK1...Internal clock output)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
SCK1 cycle time	tkcY11	$4.5 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	800			ns
		2.7 V ≤ V <sub>DD</sub> < 4.5 V	1,600			ns
SCK1 high-/low-level width	tkH11, tkL11	V <sub>DD</sub> = 4.5 to 5.5 V	tkcy11/2 - 50			ns
			tксү11/2 - 100			ns
SI1 setup time (to SCK1↑)	tsik11	$4.5 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	100			ns
		2.7 V ≤ V <sub>DD</sub> < 4.5 V	150			ns
SI1 hold time (from SCK1↑)	tksi11		400			ns
SO1 output delay time from SCK1↓	<b>t</b> KSO11	C = 100 pF <sup>Note</sup>			300	ns
STB↑ from SCK1↑	tsbD		tксү11/2 - 100		tксү11/2 + 100	ns
Strobe signal high-level width	tssw	2.7 V ≤ V <sub>DD</sub> < 5.5 V	tксү11 - 30		tксү11 + 30	ns
Busy signal setup time (to busy signal detection timing)	tBYS		100			ns
Busy signal hold time	tвүн	4.5 V ≤ V <sub>DD</sub> ≤ 5.5 V	100			ns
(from busy signal detection timing)		2.7 V ≤ V <sub>DD</sub> < 4.5 V	150			ns
SCK1↓ from busy inactive	tsps				2tксү11	ns

**Note** C is the load capacitance of the  $\overline{SCK1}$  and SO1 output lines.

# (iv) 3-wire serial I/O mode with automatic transmit/receive function (SCK1...External clock input)

Parameter	Symbol	Con	ditions	MIN.	TYP.	MAX.	Unit
SCK1 cycle time	tKCY12	$4.5 \text{ V} \leq \text{V}_{\text{DD}} \leq 5.5$	V	800			ns
		$2.7 \text{ V} \leq \text{V}_{DD} < 4.5 \text{ V}$		1,600			ns
SCK1 high-/low-level width	<b>t</b> KH12,	4.5 V ≤ V <sub>DD</sub> ≤ 5.5 V		400			ns
	<b>t</b> KL12	2.7 V ≤ V <sub>DD</sub> < 4.5	2.7 V ≤ V <sub>DD</sub> < 4.5 V				ns
SI1 setup time (to <del>SCK1</del> ↑)	tsik12	V <sub>DD</sub> = 2.7 to 5.5 V		100			ns
SI1 hold time (from SCK1↑)	<b>t</b> KSI12			400			ns
SO1 output delay time from SCK1↓	<b>t</b> KSO12	C = 100 pF <sup>Note</sup>	V <sub>DD</sub> = 2.7 to 5.5 V			300	ns
SCK1 rise/fall time	t <sub>R12</sub> , t <sub>F12</sub>	When using external device expansion function				160	ns
		When not using e expansion function				1,000	ns

Note C is the load capacitance of the SO1 output line.

### (c) Serial interface channel 2

# (i) 3-wire serial I/O mode (SCK2...Internal clock output)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
SCK2 cycle time	<b>t</b> KCY13	$4.5 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	800			ns
		$2.7 \text{ V} \leq \text{V}_{DD} < 4.5 \text{ V}$	1,600			ns
SCK2 high-/low-level width	<b>t</b> кн13,	V <sub>DD</sub> = 4.5 to 5.5 V	tксү13/2 - 50			ns
	<b>t</b> KL13		tксүтз/2 - 100			ns
SI2 setup time (to \$\overline{SCK2}\overline{\chi}\$)	<b>t</b> SIK13	$4.5~V \leq V_{DD} \leq 5.5~V$	100			ns
		$2.7 \text{ V} \leq \text{V}_{DD} < 4.5 \text{ V}$	150			ns
SI2 hold time (from \$\overline{SCK2}\overline{\cappa}\$)	<b>t</b> KSI13		400			ns
SO2 output delay time from $\overline{\text{SCK2}} \downarrow$	<b>t</b> KSO13	C = 100 pF <sup>Note</sup>			300	ns

Note C is the load capacitance of the SO2 output line.

# (ii) 3-wire serial I/O mode (SCK2...External clock input)

Parameter	Symbol	Coi	nditions	MIN.	TYP.	MAX.	Unit
SCK2 cycle time	tkCY14	4.5 V ≤ V <sub>DD</sub> ≤ 5.5	V	800			ns
		2.7 V ≤ V <sub>DD</sub> < 4.5	V	1,600			ns
SCK2 high-/low-level width	<b>t</b> кн14,	4.5 V ≤ V <sub>DD</sub> ≤ 5.5	4.5 V ≤ V <sub>DD</sub> ≤ 5.5 V				ns
	t <sub>KL14</sub>	2.7 V ≤ V <sub>DD</sub> < 4.5	V	800			ns
SI2 setup time (to \$\overline{SCK2}\dagger\$)	tsik14	V <sub>DD</sub> = 2.7 to 5.5 V		100			ns
SI2 hold time (from SCK2↑)	tksi14			400			ns
SO2 output delay time from SCK2↓	<b>t</b> KSO14	C = 100 pF <sup>Note</sup>	V <sub>DD</sub> = 2.7 to 5.5 V			300	ns
SCK2 rise/fall time	t <sub>R14</sub> ,	Other than below	,			160	ns
	tF14	V <sub>DD</sub> = 4.5 to 5.5 V When not using external device expansion function				1	μs

Note C is the load capacitance of the SO2 output line.



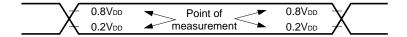
# (iii) UART mode (Dedicated baud rate generator output)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Transfer rate		$4.5 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$			78,125	bps
		$2.7 \text{ V} \leq \text{V}_{DD} < 4.5 \text{ V}$			39,063	bps

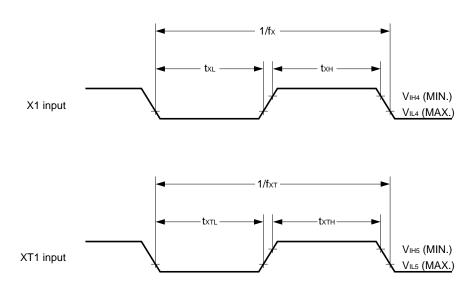
# (iv) UART mode (External clock input)

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
ASCK cycle time	tKCY15	$4.5 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	800			ns
		2.7 V ≤ V <sub>DD</sub> < 4.5 V	1,600			ns
ASCK high-/low-level width	<b>t</b> KH15, <b>t</b> KL15	$4.5 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$	400			ns
		2.7 V ≤ V <sub>DD</sub> < 4.5 V	800			ns
Transfer rate		$4.5 \text{ V} \leq \text{V}_{DD} \leq 5.5 \text{ V}$			39,063	bps
		2.7 V ≤ V <sub>DD</sub> < 4.5 V			19,531	bps
ASCK rise/fall time	t <sub>R15</sub> , t <sub>F15</sub>	V <sub>DD</sub> = 4.5 to 5.5 V,			1,000	ns
		when not using external device				
		expansion function.				
					160	ns

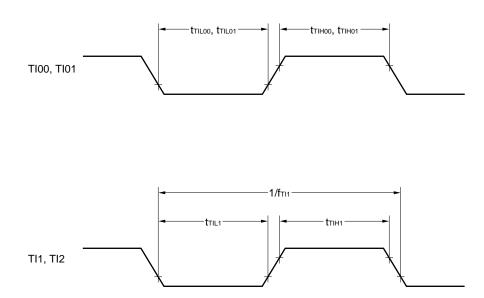
# AC Timing Measurement Points (Excluding X1, XT1 Inputs)



# **Clock Timing**

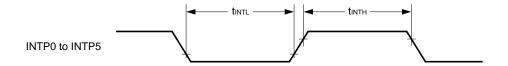


# **TI Timing**

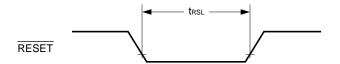




# **Interrupt Request Input Timing**

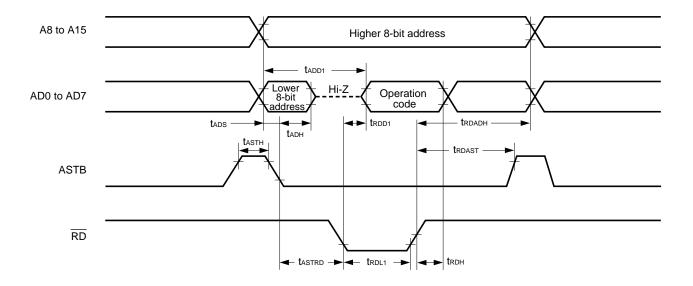


# **RESET** Input Timing

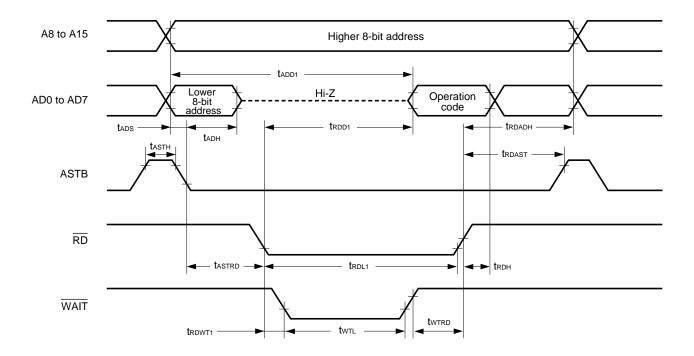


### **Read/Write Operation**

### External fetch (no wait):

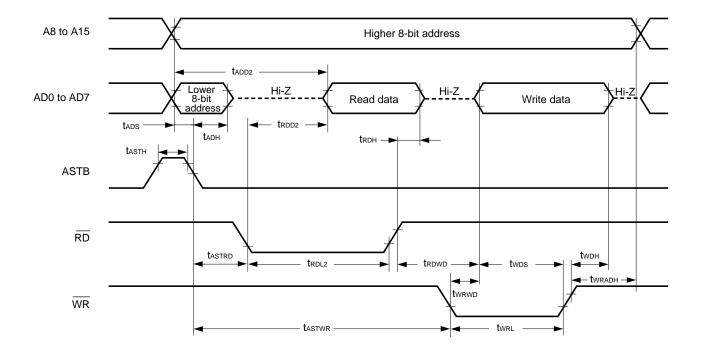


# External fetch (wait insertion):

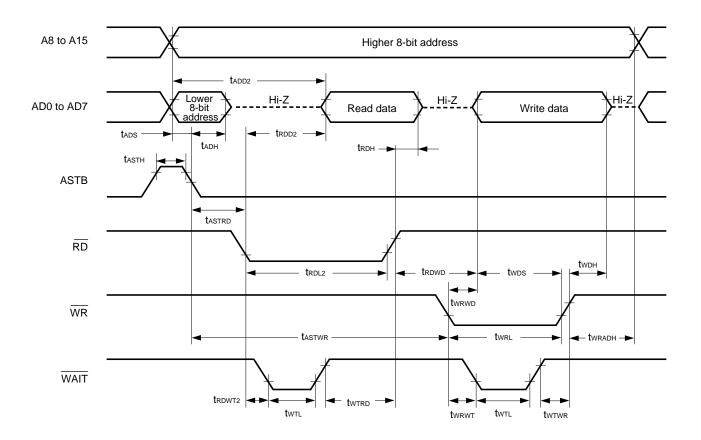




### External data access (no wait):



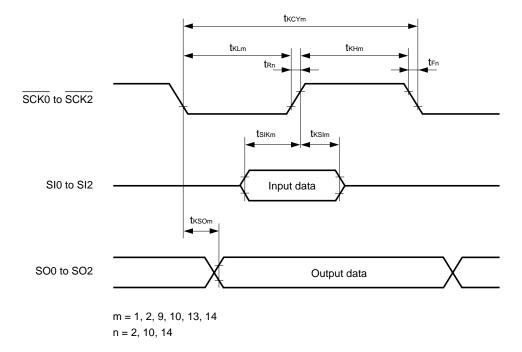
### External data access (wait insertion):



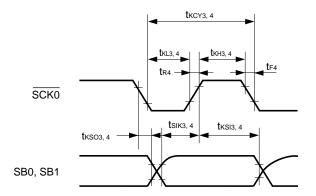


### **Serial Transfer Timing**

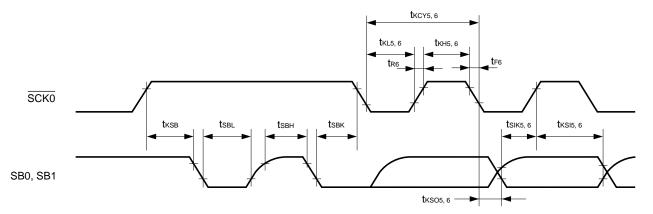
### 3-wire serial I/O mode:



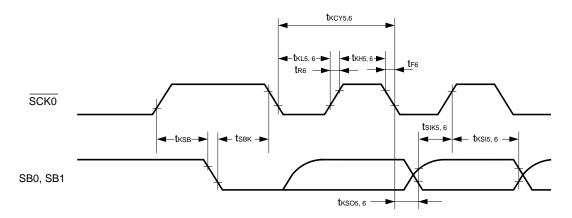
### 2-wire serial I/O mode:



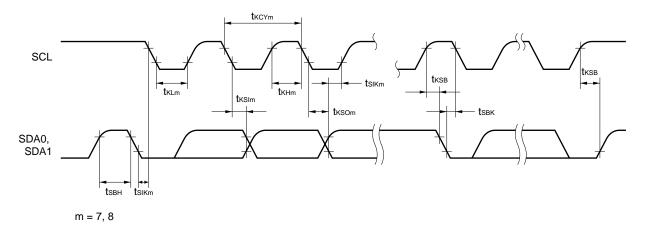
# SBI mode (bus release signal transfer):



# SBI mode (command signal transfer):

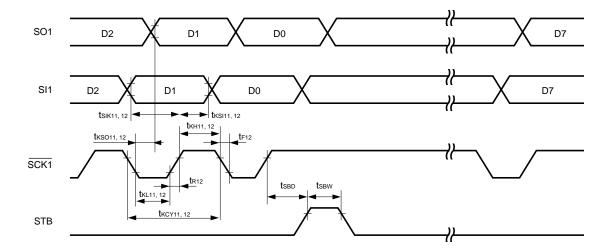


### I<sup>2</sup>C bus mode:

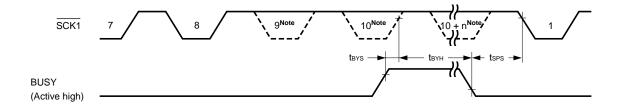




3-wire serial I/O mode with automatic transmit/receive function:

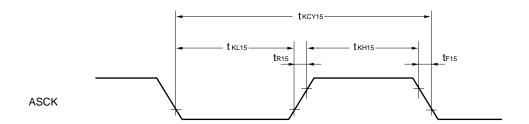


3-wire serial I/O mode with automatic transmit/receive function (busy processing):



**Note** The signal is not actually driven low here; it is shown as such to indicate the timing.

### **UART mode (external clock input):**





### A/D Converter Characteristics ( $T_A = -40 \text{ to } +85^{\circ}\text{C}$ , $V_{DD} = 2.7 \text{ to } 5.5 \text{ V}$ , $AV_{SS} = V_{SS} = 0 \text{ V}$ )

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution			8	8	8	bit
Overall error <sup>Note 1</sup>		2.7 V ≤ AV <sub>REF0</sub> < 4.5 V			±1.0	%
		4.5 V ≤ AV <sub>REF0</sub> < 5.5 V			±0.6	%
Conversion time	TCONV	2.7 V ≤ AV <sub>REF0</sub> < 5.5 V	16		100	μs
Analog input voltage	VIAN		AVss		AV <sub>REF0</sub>	V
Reference voltage	AV <sub>REF0</sub>		2.7		V <sub>DD</sub>	V
AVREFO current	I <sub>REF0</sub>	When A/D converter is operating Note 2		500	1,500	μΑ
		When A/D converter is not operating Note 3		0	3	μΑ

Notes 1. Excludes quantization error (±1/2 LSB). This value is indicated as a ratio to the full-scale value.

- 2. The current flowing to the AVREFO pin when bit 7 (CS) of the A/D converter mode register (ADM) is 1.
- 3. The current flowing to the AVREFO pin when bit 7 (CS) of the A/D converter mode register (ADM) is 0.

### D/A Converter Characteristics ( $T_A = -40 \text{ to } +85^{\circ}\text{C}$ , $V_{DD} = 2.7 \text{ to } 5.5 \text{ V}$ , $AV_{SS} = V_{SS} = 0 \text{ V}$ )

Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Resolution					8	bit
Overall error		$R = 2 M\Omega^{\text{Note 1}}$			±1.2	%
		$R = 4 M\Omega^{\text{Note 1}}$			±0.8	%
		R = 10 M $\Omega$ <sup>Note 1</sup>			±0.6	%
Settling time		C = 30 pF <sup>Note 1</sup>			15	μs
Output resistance	Ro	Note 2		8		kΩ
Analog reference voltage	AV <sub>REF1</sub>		1.8		V <sub>DD</sub>	V
AV <sub>REF1</sub> current	I <sub>REF1</sub>	Note 2			2.5	mA
Resistance between AVREF1 and AVSS	RAIREF1	DACS0, DACS1 = 55H <sup>Note 2</sup>	4	8		kΩ

Notes 1. R and C are the D/A converter output pin load resistance and load capacitance, respectively.

2. Value for one D/A converter channel

Remark DACS0 and DACS1: D/A conversion value setting registers 0, 1



#### Data Memory STOP Mode Low Supply Voltage Data Retention Characteristics (TA = -40 to +85°C)

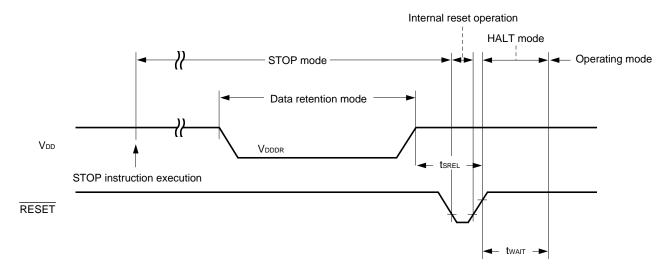
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
Data retention power supply voltage	VDDDR		1.8		5.5	V
Data retention power supply current	Idddr	V <sub>DDDR</sub> = 1.8 V Subsystem clock stop and feed-back resistor disconnected		0.1	10	μΑ
Release signal set time	tsrel		0			μs
Oscillation stabilization	twait	Release by RESET		217/fx		ms
wait time		Release by interrupt request		Note		ms

**Note** Selection of 2<sup>12</sup>/fxx and 2<sup>14</sup>/fxx to 2<sup>17</sup>/fxx is possible with bits 0 to 2 (OSTS0 to OSTS2) of the oscillation stabilization time select register (OSTS).

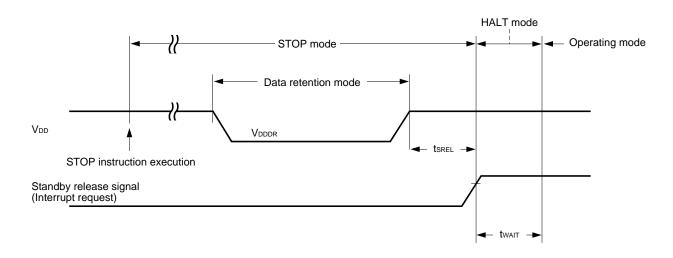
**Remark** fxx: Main system clock frequency (fx or fx/2)

fx: Main system clock oscillation frequency

## Data Retention Timing (STOP Mode Release by RESET)



### Data Retention Timing (Standby Release Signal: STOP Mode Release by Interrupt Request Signal)





### Flash Memory Programming Characteristics ( $V_{DD}$ = 2.7 to 5.5 V, $T_A$ = 10 to 40°C)

#### (1) Write/delete characteristics

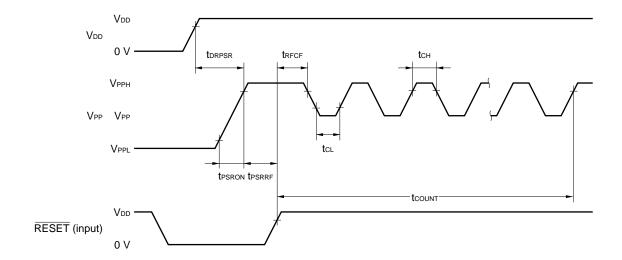
Parameter	Symbol		Conditions	MIN.	TYP.	MAX.	Unit
Write current (V <sub>DD</sub> pin) <sup>Note 1</sup>	toow	When VPP = VPP1	5.0 MHz crystal oscillation operation mode (fxx = 2.5 MHz)Note 2			15.5	mA
			5.0 MHz crystal oscillation operation mode (fxx = 5.0 MHz) <sup>Note 3</sup>			28.7	mA
Write current (VPP pin)Note 1	IPPW	When VPP = VPP1	5.0 MHz crystal oscillation operation mode (fxx = 2.5 MHz)Note 2			19.5	mA
			5.0 MHz crystal oscillation operation mode (fxx = 5.0 MHz)Note 3			32.7	mA
Delete current (V <sub>DD</sub> pin) <sup>Note 1</sup>	IDDE	When V <sub>PP</sub> = V <sub>PP1</sub>	5.0 MHz crystal oscillation operation mode (fxx = 2.5 MHz) <sup>Note 2</sup>			15.5	mA
			5.0 MHz crystal oscillation operation mode (fxx = 5.0 MHz) <sup>Note 3</sup>			28.7	mA
Delete current (VPP pin)Note 1	IPPE	When VPP = VPP1				100	mA
Unit delete time	ter			0.5	1	1	s
Total delete time	tera					20	S
Number of overwrite	Cwrt	Delete and write ar	e counted as one cycle			20	times
VPP power supply voltage	V <sub>PP0</sub>	In normal mode		0		0.2 V <sub>DD</sub>	V
	V <sub>PP1</sub>	At flash memory pr	ogramming	9.7	10.0	10.3	V

- Notes 1. 1. AVREF current and Port current (current flowing to internal pull-up resistor) are not included.
  - **2.** When main system clock is operating at fxx = fxx/2 (when oscillation mode selection resistor (OSMS) is set to 00H).
  - **3.** When main system clock is operating at fxx = fxx (when OSMS is set to 01H).

### 2) Serial write operation characteristics

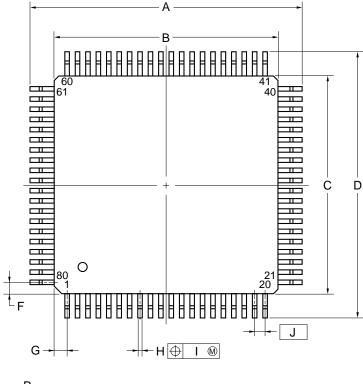
Parameter	Symbol	Conditions	MIN.	TYP.	MAX.	Unit
VPP setup time	tpsron	V <sub>PP</sub> high voltage	1.0			μs
V <sub>PP</sub> ↑ setup time from V <sub>DD</sub> ↑	<b>t</b> DRPSR	V <sub>PP</sub> high voltage	1.0			μs
RESET↑ setup time from V <sub>PP</sub> ↑	<b>t</b> psrrf	V <sub>PP</sub> high voltage	1.0			μs
V <sub>PP</sub> count start time from RESET↑	trfcf		1.0			μs
Count execution time	tcount				2.0	ms
V <sub>PP</sub> counter high-level width	tсн		8.0			μs
V <sub>PP</sub> counter low-level width	tcL		8.0			μs
VPP counter noise elimination width	tnfw			40		ns

# Flash Write Mode Setting Timing

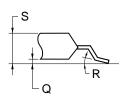


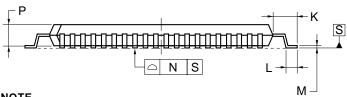
### 8. PACKAGE DRAWINGS

# 80-PIN PLASTIC QFP (14x14)



detail of lead end



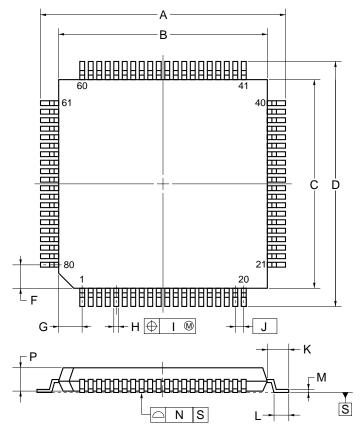


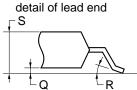
NOTE

Each lead centerline is located within 0.13 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
Α	17.20±0.20
В	14.00±0.20
С	14.00±0.20
D	17.20±0.20
F	0.825
G	0.825
Н	0.32±0.06
I	0.13
J	0.65 (T.P.)
K	1.60±0.20
L	0.80±0.20
М	$0.17^{+0.03}_{-0.07}$
N	0.10
Р	1.40±0.10
Q	0.125±0.075
R	3°+7° -3°
S	1.70 MAX.
	P80GC-65-8BT-1

# 80 PIN PLASTIC TQFP (FINE PITCH) (12x12)





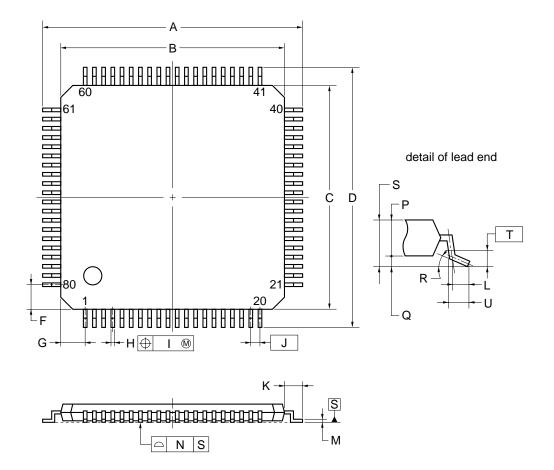
#### NOTE

Each lead centerline is located within 0.10 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
Α	14.00±0.20
В	12.00±0.20
С	12.00±0.20
D	14.00±0.20
F	1.25
G	1.25
Н	$0.22^{+0.05}_{-0.04}$
I	0.10
J	0.50 (T.P.)
K	1.00±0.20
L	0.50±0.20
М	$0.145^{+0.055}_{-0.045}$
N	0.10
Р	1.05±0.07
Q	0.10±0.05
R	5°±5°
S	1.27 MAX.
	DOGGIC EG DEG

P80GK-50-BE9-6

# **★** 80-PIN PLASTIC TQFP (FINE PITCH) (12x12)



#### NOTE

Each lead centerline is located within 0.08 mm of its true position (T.P.) at maximum material condition.

ITEM	MILLIMETERS
Α	14.0±0.2
В	12.0±0.2
С	12.0±0.2
D	14.0±0.2
F	1.25
G	1.25
Н	0.22±0.05
I	0.08
J	0.5 (T.P.)
K	1.0±0.2
L	0.5
M	0.145±0.05
N	0.08
Р	1.0
Q	0.1±0.05
R	3°+4°
S	1.1±0.1
T	0.25
U	0.6±0.15
	P80GK-50-9EU-

P80GK-50-9EU-

#### 9. RECOMMENDED SOLDERING CONDITIONS

The  $\mu$ PD78F0058 and 78F0058Y should be soldered and mounted under the following recommended conditions.

For the details of the recommended soldering conditions, refer to the document **Semiconductor Device Mounting Technology Manual (C10535E)**.

For soldering methods and conditions other than those recommended below, contact your NEC sales representative.

Table 9-1. Surface Mounting Type Soldering Conditions

 $\mu \text{PD78F0058GC-8BT}$  : 80-pin plastic QFP (14 × 14 mm)  $\mu \text{PD78F0058YGC-8BT}$  : 80-pin plastic QFP (14 × 14 mm)

Soldering	Soldering Conditions	Recommended
Method		Condition Symbol
Infrared reflow	Package peak temperature: 235°C, Time: 30 seconds max. (at 210°C or higher),	IR35-00-2
	Count: Twice or less	
VPS	Package peak temperature: 215°C, Time: 40 seconds max. (at 200°C or higher),	VP15-00-2
	Count: Twice or less	
Wave soldering	Solder bath temperature: 260°C max., Time: 10 seconds max., Count: Once,	WS60-00-1
	Preheating temperature: 120°C max. (package surface temperature)	
Partial heating	Pin temperature: 300°C max., Time: 3 seconds max. (per pin row)	_

Caution Do not use different soldering methods together (except for partial heating).

 $\mu$ PD78F0058GK-BE9: 80-pin plastic TQFP (12 × 12 mm, resin thickness 1.05 mm)  $\mu$ PD78F0058YGK-BE9: 80-pin plastic TQFP (12 × 12 mm, resin thickness 1.05 mm)

Soldering	Soldering Conditions	Recommended
Method		Condition Symbol
Infrared reflow	Package peak temperature: 235°C, Time: 30 seconds max. (at 210°C or higher),	IR35-107-2
	Count: Twice or less, Exposure limit: 7 days <sup>Note</sup>	
	(after 7 days, prebake at 125°C for 10 hours)	
VPS	Package peak temperature: 215°C, Time: 40 seconds max. (at 200°C or higher),	VP15-107-2
	Count: Twice or less, Exposure limit: 7 days <sup>Note</sup>	
	(after 7 days, prebake at 125°C for 10 hours)	
Wave soldering	-	_
Partial heating	Pin temperature: 300°C max., Time: 3 seconds max. (per pin row)	_

Note After opening the dry pack, store it at 25°C or less and 65% RH or less for the allowable storage period.

Caution Do not use different soldering methods together (except for partial heating).



 $\mu$ PD78F0058GK-9EU : 80-pin plastic TQFP (12  $\times$  12 mm, resin thickness 1.0 mm)  $\mu$ PD78F0058YGK-9EU : 80-pin plastic TQFP (12  $\times$  12 mm, resin thickness 1.0 mm)

Soldering	Soldering Conditions	Recommended
Method		Condition Symbol
Infrared reflow	Undefined	Undefined
VPS	Undefined	Undefined
Wave soldering	Undefined	Undefined
Partial heating	Pin temperature: 300°C max., Time: 3 seconds max. (per pin row)	_

### **★** APPENDIX A. DEVELOPMENT TOOLS

The following development tools are available for system development using the  $\mu$ PD780058, 780058Y Subseries.

Also, refer to (5) Cautions on using development tools.

### (1) Language processing software

RA78K0	Assembler package common to the 78K/0 Series
CC78K0	C compiler package common to the 78K/0 Series
DF780058	Device file for the μPD780058, 780058Y Subseries
CC78K0-L	C compiler library source file common to the 78K/0 Series

### (2) Flash memory writing tools

Flashpro III (Part number: Dedicated flash programmer for microcontrollers incorporating flash memory		Dedicated flash programmer for microcontrollers incorporating flash memory
FL-PR3, PG-FL3)		
	FA-80GC-8BT	Adapter for flash memory writing
	FA-80GK	
	FA-80GK-9EU	

### (3) Debugging tools

#### • When using the IE-78K0-NS in-circuit emulator

IE-78K0-NS	In-circuit emulator common to the 78K/0 Series	
IE-70000-MC-PS-B	Power supply unit for IE-78K0-NS	
IE-78K0-NS-PA	Performance board to enhance and expand the functions of the IE-78K0-NS	
IE-70000-98-IF-C	Adapter used when a PC-9800 series PC (except notebook PC) is used as the host machine (C bus supported)	
IE-70000-CD-IF-A	PC card and interface cable used when a PC-9800 series notebook PC is used as the host machine (PCMCIA socket supported)	
IE-70000-PC-IF-C	Adapter necessary when an IBM PC/AT <sup>TM</sup> -compatible is used as the host machine (ISA bus supported)	
IE-70000-PCI-IF	Interface adapter necessary when using a PC with PCI bus as the host machine	
IE-780308-NS-EM1	Emulation board common to the $\mu$ PD780308 Subseries	
NP-80GC	Emulation probe for 80-pin plastic QFP (GC-8BT type)	
NP-80GK	Emulation probe for 80-pin plastic TQFP (GK-BE9, GK-9EU type)	
TGK-080SDW	Conversion adapter to connect the NP-80GK and a target system board on which 80-pin plastic TQFP (GK-BE9, GK-9EU type) can be mounted	
EV-9200GC-80	Socket to be mounted on a target system board made for 80-pin plastic QFP (GC-8BT type)	
ID78K0-NS	Integrated debugger for IE-78K0-NS	
SM78K0	System simulator common to the 78K/0 Series	
DF780058	Device file for the $\mu$ PD780058, 780058Y Subseries	

# • When using the IE-78001-R-A in-circuit emulator

IE-78001-R-A	In-circuit emulator common to the 78K/0 Series
IE-70000-98-IF-C	Adapter used when PC-9800 series PC (except notebook type) is used as host machine (C bus supported)
IE-70000-PC-IF-C	Interface adapter when using IBM PC/AT-compatible as the host machine (ISA bus supported)
IE-78000-R-SV3	Interface adapter and cable used when EWS is used as the host machine
IE-780308-NS-EM1 IE-780308-R-EM	Emulation board common to the $\mu$ PD780308 Subseries
IE-78K0-R-EX1	Emulation probe conversion board necessary when using the IE-780308-NS-EM1 on the IE-78001-R-A.
EP-78230GC-R	Emulation probe for 80-pin plastic QFP (GC-8BT type)
EP-78054GK-R	Emulation probe for 80-pin plastic TQFP (GK-BE9, GK-9EU type)
TGK-080SDW	Conversion adapter to connect the EP-78054GK-R and a target system on which an 80-pin plastic TQFP (GK-BE9, GK-9EU type) can be mounted
EV-9200GC-80	Socket to be mounted on a target system board made for 80-pin plastic QFP (GC-8BT type)
ID78K0	Integrated debugger for IE-78001-R-A
SM78K0	78K/0 Series common system simulator
DF780058	Device file for the μPD780058, 780058Y Subseries

# (4) Real-time OS

RX78K/0	Real-time OS for the 78K/0 Series
MX78K0	OS for the 78K/0 Series

#### (5) Cautions on using development tools

- The ID78K0-NS, ID78K0, and SM78K0 are used in combination with the DF780058.
- The CC78K0 and RX78K/0 are used in combination with the RA78K0 and DF780058.
- The FL-PR3, FA-80GC-8BT, FA-80GK, FA80GK-9EU, NP-80GC, and NP-80GK are products of Naito Densei Machida Mfg. Co., Ltd. (TEL: +81-44-822-3813). Contact an NEC distributor regarding the purchase of these products.
- TGK-080SDW is a product made by Tokyo Eletech Corp.

For further information, contact Daimaru Kogyo, Ltd.

Electronics Department (Tokyo) (TEL: +81-3-3820-7112)

Electronics 2nd Department (Osaka) (TEL: +81-6-6244-6672)

- For third-party development tools, see the Single-Chip Microcontroller Development Tool Selection Guide (U11069E)
- The host machine and OS suitable for each software are as follows:

Host Machine [OS]	PC	EWS
	PC-9800 Series [Japanese Windows™]	HP9000 series 700™ [HP-UX™]
	IBM PC/AT-compatible	SPARCstation™ [SunOS™ ,Solaris™]
Software	[Japanese/English Windows]	NEWS <sup>™</sup> (RISC) [NEWS-OS <sup>™</sup> ]
RA78K0	√Note	$\checkmark$
CC78K0	√Note	$\checkmark$
ID78K0-NS	V	-
ID78K0	V	$\checkmark$
SM78K0	V	_
RX78K/0	√Note	V
MX78K0	√Note	V

Note DOS-based software

### **★** APPENDIX B. RELATED DOCUMENTS

The related documents indicated in this publication may include preliminary versions. However, preliminary versions are not marked as such.

#### **Documents Related to Devices**

Document Name D		cument No.	
	Japanese	English	
μPD780058, 780058Y Subseries User's Manual	U12013J	U12013E	
μPD780053, 780054, 780055, 780056, 780058 Data Sheet	U12182J	U12182E	
μPD78F0058, 78F0058Y Data Sheet	U12092J	This document	
78K/0 Series User's Manual - Instruction	U12326J	U12326E	
78K/0 Series Instruction Table	U10903J	_	
78K/0 Series Instruction Set	U10904J	_	
78K/0, 78K/0S Series Flash Memory Write Application Note	U14458J	U14458E	

### **Documents Related to Development Tools (User's Manuals)**

Document Name	Document No.		
		Japanese	English
RA78K0 Assembler Package	Operation	U11802J	U11802E
	Assembly Language	U11801J	U11801E
	Structured Assembly Language	U11789J	U11789E
RA78K Series Structured Assembler Preprocessor	,	U12323J	EEU-1402
CC78K0 C Compiler	Operation	U11517J	U11517E
	Language	U11518J	U11518E
IE-78K0-NS		U13731J	U13731E
IE-78001-R-EM		To be prepared	To be prepared
IE-780308-NS-EM1		To be prepared	To be prepared
IE-780308-R-EM		U11362J	U11362E
EP-78230		EEU-985	EEU-1515
EP-78054GK-R	EP-78054GK-R		_
SM78K0 System Simulator Windows Based	Reference	U10181J	U10181E
SM78K Series System Simulator	External Part User Open Interface Specifications	U10092J	U10092E
ID78K0-NS Integrated Debugger Windows Based	Reference	U12900J	U12900E
ID78K0 Integrated Debugger EWS Based	Reference	U11151J	_
ID78K0 Integrated Debugger PC Based	Reference	U11539J	U11539E
ID78K0 Integrated Debugger Windows Based	Guide	U11649J	U11649E

Caution The related documents listed above are subject to change without notice. Be sure to use the latest version of each document for designing.

#### **Documents Related to Embedded Software (User's Manuals)**

Document Name		Document No.	
		Japanese	English
78K/0 Series Real-Time OS	Fundamentals	U11537J	U11537E
	Installation	U11536J	U11536E
78K/0 Series OS MX78K0	Fundamental	U12257J	U12257E

#### **Other Related Documents**

Document Name	Document No.	
	Japanese	English
SEMICONDUCTORS SELECTION GUIDE Products & Packages (CD-ROM)	X13769X	
Semiconductor Device Mounting Technology Manual	C10535J	C10535E
Quality Grades on NEC Semiconductor Devices	C11531J	C11531E
NEC Semiconductor Device Reliability/Quality Control System	C10983J	C10983E
Guide to Prevent Damage for Semiconductor Devices by Electrostatic Discharge (ESD)	C11892J	C11892E
Guide to Microcomputer-Related Products by Third Party	U11416J	_

Caution The related documents listed above are subject to change without notice. Be sure to use the latest version of each document for designing.

#### **NOTES FOR CMOS DEVICES -**

#### 1 PRECAUTION AGAINST ESD FOR SEMICONDUCTORS

Note:

Strong electric field, when exposed to a MOS device, can cause destruction of the gate oxide and ultimately degrade the device operation. Steps must be taken to stop generation of static electricity as much as possible, and quickly dissipate it once, when it has occurred. Environmental control must be adequate. When it is dry, humidifier should be used. It is recommended to avoid using insulators that easily build static electricity. Semiconductor devices must be stored and transported in an anti-static container, static shielding bag or conductive material. All test and measurement tools including work bench and floor should be grounded. The operator should be grounded using wrist strap. Semiconductor devices must not be touched with bare hands. Similar precautions need to be taken for PW boards with semiconductor devices on it.

### (2) HANDLING OF UNUSED INPUT PINS FOR CMOS

Note:

No connection for CMOS device inputs can be cause of malfunction. If no connection is provided to the input pins, it is possible that an internal input level may be generated due to noise, etc., hence causing malfunction. CMOS devices behave differently than Bipolar or NMOS devices. Input levels of CMOS devices must be fixed high or low by using a pull-up or pull-down circuitry. Each unused pin should be connected to VDD or GND with a resistor, if it is considered to have a possibility of being an output pin. All handling related to the unused pins must be judged device by device and related specifications governing the devices.

#### (3) STATUS BEFORE INITIALIZATION OF MOS DEVICES

Note:

Power-on does not necessarily define initial status of MOS device. Production process of MOS does not define the initial operation status of the device. Immediately after the power source is turned ON, the devices with reset function have not yet been initialized. Hence, power-on does not guarantee out-pin levels, I/O settings or contents of registers. Device is not initialized until the reset signal is received. Reset operation must be executed immediately after power-on for devices having reset function.

Purchase of NEC I<sup>2</sup>C components conveys a license under the Philips I<sup>2</sup>C Patent Rights to use these components in an I<sup>2</sup>C system, provided that the system conforms to the I<sup>2</sup>C Standard Specification as defined by Philips.

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- · Device availability
- · Ordering information
- · Product release schedule
- Availability of related technical literature
- Development environment specifications (for example, specifications for third-party tools and components, host computers, power plugs, AC supply voltages, and so forth)
- · Network requirements

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